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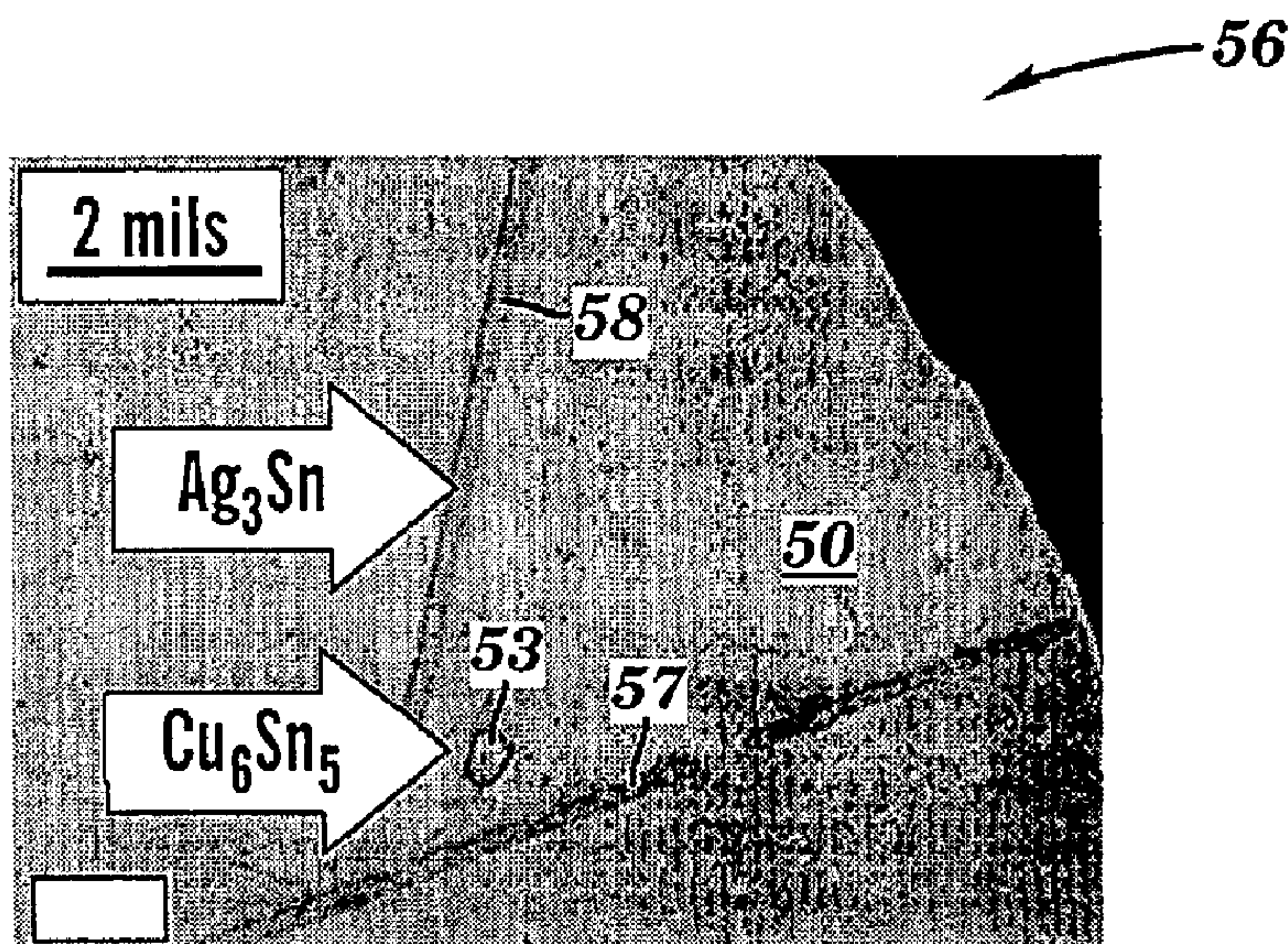
(54) Titre : COMPOSITION DE BRASURE CONTENANT UN ALLIAGE SANS PLOMB D'ETAIN-ARGENT-CUIVRE
(54) Title: LEAD-FREE TIN-SILVER-COPPER ALLOY SOLDER COMPOSITION



(57) Abrégé/Abstract:
A solder composition and associated method of formation. The solder composition comprises a substantially lead-free alloy that includes tin (Sn), silver (Ag), and copper. The tin has a weight percent concentration in the alloy of at least about 90 %. The silver has a weight percent concentration X in the alloy. X is sufficiently small that formation of Ag_3Sn plates (57, 58) is substantially suppressed when the alloy in a liquefied state is being solidified by being cooled to a lower temperature at which the solid Sn phase is nucleated. This lower temperature corresponds to an undercooling δT relative to the eutectic melting temperature of the alloy. Alternatively, X may be about 4.0 % or less, wherein the liquefied alloy is cooled at a cooling rate that is high enough to substantially suppress Ag_3Sn plate (57, 58) formation in the alloy. The copper has a weight percent concentration in the alloy not exceeding about 1.5 %.

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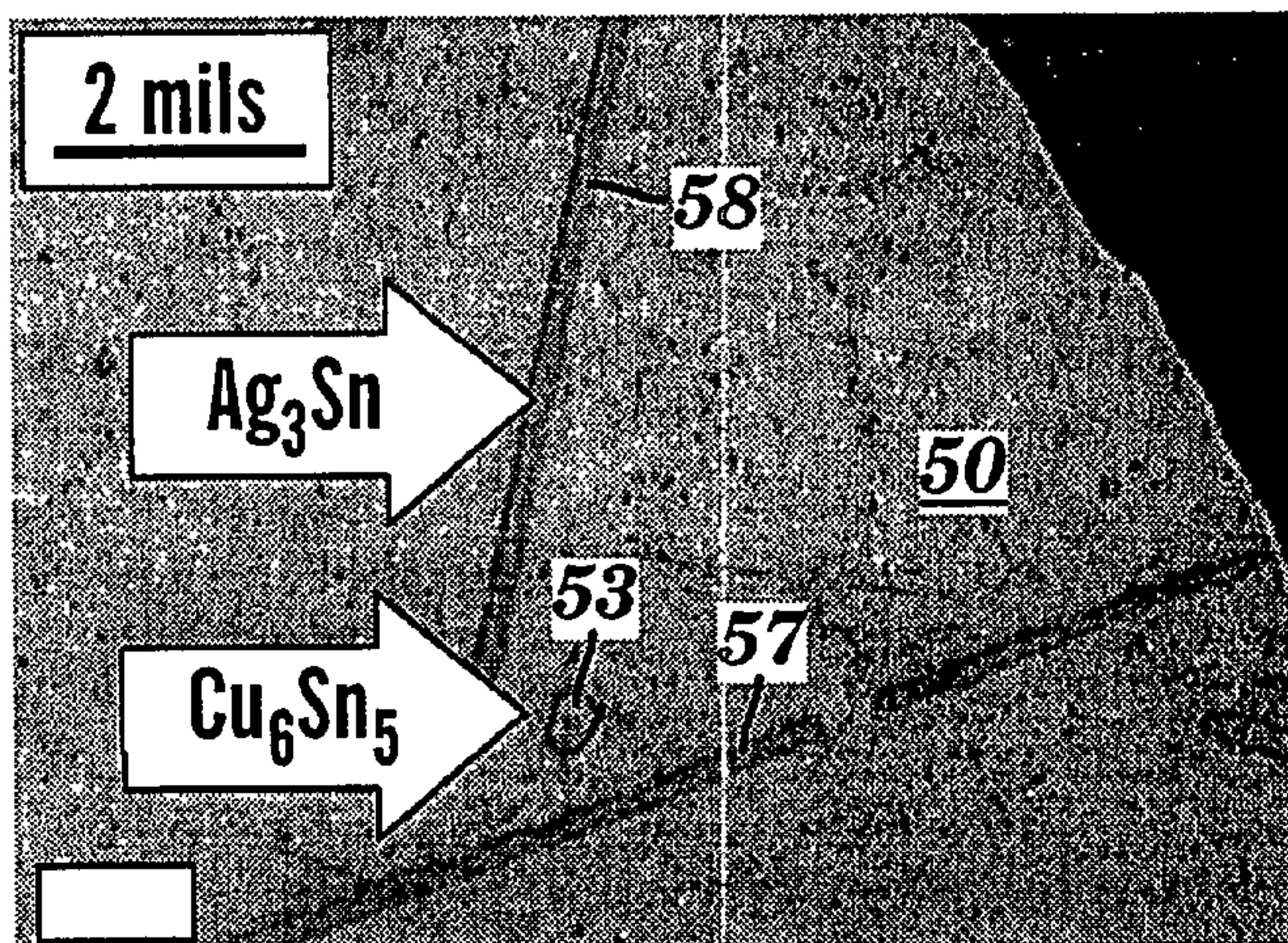

(57) Abstract: A solder composition and associated method of formation. The solder composition comprises a substantially lead-free alloy that includes tin (Sn), silver (Ag), and copper. The tin has a weight percent concentration in the alloy of at least about 90 %. The silver has a weight percent concentration X in the alloy. X is sufficiently small that formation of Ag_3Sn plates (57, 58) is substantially suppressed when the alloy in a liquefied state is being solidified by being cooled to a lower temperature at which the solid Sn phase is nucleated. This lower temperature corresponds to an undercooling δT relative to the eutectic melting temperature of the alloy. Alternatively, X may be about 4.0 % or less, wherein the liquefied alloy is cooled at a cooling rate that is high enough to substantially suppress Ag_3Sn plate (57, 58) formation in the alloy. The copper has a weight percent concentration in the alloy not exceeding about 1.5 %.

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LEAD-FREE TIN-SILVER-COPPER ALLOY SOLDER COMPOSITION

Background of the Invention

1. Technical Field

The present invention relates generally to a lead-free alloy solder composition and more specifically to a tin-silver-copper alloy solder composition.

2. Related Art

A chip carrier may be coupled to a circuit card by a ball grid array (BGA) comprising BGA solder balls. Such BGA solder balls have typically comprised a eutectic alloy composition of 63% tin (Sn) and 37% lead (Pb) which has a low melting temperature of 183 °C and is highly reliable. Unfortunately, lead is toxic and environmentally hazardous. As a result, lead-free solders are now beginning to be used commercially. However, many low-melt, lead-free solders have adverse physical characteristics which may cause reliability problems. Thus, there is a need for a reliable low-melt, substantially lead-free solder ball for coupling a chip or chip carrier to the next level of assembly (e.g., coupling a chip carrier to a circuit card).

Summary of the Invention

In first embodiments, the present invention provides a solder composition, comprising a solder alloy,

wherein the alloy is substantially free of lead,

wherein the alloy includes tin (Sn), silver (Ag), and copper (Cu),

wherein the tin has a weight percent concentration in the alloy of at least about 90%,

wherein the silver has a weight percent concentration of X in the alloy,

wherein X is sufficiently small that formation of Ag_3Sn plates is substantially suppressed when the alloy in a liquefied state is being solidified by being cooled at to a lower temperature at which the solid Sn phase is nucleated,

wherein the lower temperature corresponds to an undercooling δT relative to the eutectic melting temperature of the alloy, and

wherein the copper has a weight percent concentration in the alloy not exceeding about 1.5%.

In second embodiments, the present invention provides a method for forming an electrical structure, comprising:

providing a first substrate and a first solder ball attached to a first electrically conductive pad that is coupled to the first substrate, wherein the first solder ball comprises a solder alloy, wherein the alloy is substantially free of lead, wherein the alloy includes tin (Sn), silver (Ag), and copper (Cu), wherein the tin has a weight percent concentration in the alloy of at least about 90%, and wherein the copper has a weight percent concentration in the alloy not exceeding about 1.5%;

providing a second substrate and a second electrically conductive pad coupled to the second substrate;

coupling the first solder ball to the second pad;

melting the first solder ball by heating the first solder ball to form a modified solder ball; and

solidifying the modified solder ball by cooling the modified solder ball to a lower temperature at which the solid Sn phase is nucleated, and wherein the lower temperature corresponds to an undercooling δT relative to the eutectic melting temperature of the alloy, wherein the solidified modified solder ball is a solder joint that couples the first substrate to the second substrate, and wherein a silver weight percent concentration X_2 in the modified solder ball is sufficiently small that formation of Ag_3Sn plates is substantially suppressed during said cooling.

In third embodiments, the present invention provides a method for forming a solder composition, comprising:

providing a solder alloy, wherein the alloy is substantially free of lead, wherein the alloy includes tin (Sn), silver (Ag), and copper (Cu), wherein the tin has a weight percent concentration in the alloy of at least about 90%, wherein the silver has a weight percent concentration in the alloy not exceeding about 4.0%, and wherein the copper has a weight percent concentration in the alloy not exceeding about 1.5%;

melting the alloy by heating the alloy; and

solidifying the melted alloy by cooling the melted alloy at a cooling rate that is high enough to substantially suppress Ag_3Sn plate formation in the alloy during said cooling.

In fourth embodiments, the present invention provides a method for forming an electrical structure, comprising:

providing a first substrate and a first solder ball attached to a first electrically conductive pad that is coupled to the first substrate, wherein the first solder ball comprises a solder alloy, wherein the alloy is substantially free of lead, wherein the alloy includes tin (Sn), silver (Ag), and copper (Cu), wherein the tin has a weight percent concentration in the alloy of at least about 90%, wherein the silver has a weight percent concentration in the alloy not exceeding about 4.0%, and wherein the copper has a weight percent concentration in the alloy not exceeding about 1.5%;

providing a second substrate and a second electrically conductive pad coupled to the second substrate;

coupling the first solder ball to the second pad;

melting the first solder ball by heating the first solder ball to form a modified solder ball; and

solidifying the modified solder ball by cooling the modified solder ball at a cooling rate that is high enough to substantially suppress Ag_3Sn plate formation in the modified solder ball during said cooling, wherein the solidified modified solder ball is a solder joint that couples the first substrate to the second substrate.

In fifth embodiments, the present invention provides a pre-soldering electrical structure, comprising:

a first substrate and a first solder ball attached to a first electrically conductive pad that is coupled to the first substrate, wherein the first solder ball comprises a solder alloy, wherein the alloy is substantially free of lead, wherein the alloy includes tin (Sn), silver (Ag), and copper

(Cu), wherein the tin has a weight percent concentration in the alloy of at least about 90%, and wherein the copper has a weight percent concentration in the alloy not exceeding about 1.5%;

a second substrate and a second electrically conductive pad coupled to the second substrate, wherein the first solder ball is coupled to the second pad, wherein the first solder ball is adapted to being melted by being heated to form a modified solder ball, wherein the modified solder ball is adapted to being solidified by being cooled to a lower temperature at which the solid Sn phase is nucleated, wherein the lower temperature corresponds to an undercooling δT relative to the eutectic melting temperature of the alloy, wherein the solidified modified solder ball is a solder joint that couples the first substrate to the second substrate, and wherein a silver weight percent concentration X_2 in the modified solder ball is sufficiently small that formation of Ag_3Sn plates are substantially suppressed during said cooling.

In sixth embodiments, the present invention provides a post-soldering electrical structure comprising:

a first substrate; and

a second substrate, wherein the first substrate is coupled to the second substrate by a solder joint, wherein the solder joint comprises an alloy, wherein the alloy is substantially free of lead, wherein the alloy includes tin (Sn), silver (Ag), and copper (Cu), wherein the tin has a weight percent concentration in the alloy of at least about 90%, wherein the silver has a weight percent concentration in the alloy of X_2, wherein X_2 is sufficiently small that Ag_3Sn plates are substantially absent in the solder joint, and wherein the copper has a weight percent concentration in the alloy not exceeding about 1.5%.

The present invention provides a reliable low-melt, substantially lead-free solder ball for coupling a chip carrier to a circuit card, or for coupling an integrated circuit chip to a chip carrier.

Brief Description of the Drawings

FIG. 1A depicts a cross-sectional view of an electronic structure, showing a first substrate in position for being soldered to a second substrate.

FIG. 1B depicts a cross-sectional view of the electronic structure of FIG. 1 after the first substrate has been soldered to the second substrate

FIGS. 2A-2B depict cross-sectional images of a solder joint associated with a solder ball after the solder joint has been subject to thermal cycle testing.

FIGS. 3A-3B depict cross-sectional images of a solder joint associated with a ball grid array (BGA) solder ball after the solder joint has been subject to thermal cycle testing.

FIG. 3C depicts cross-sectional images of a solder joint associated with a BGA solder ball, showing crack propagation along a silver-tin plate in the solder ball following thermal cycle testing of the solder joint.

FIGS. 4A-4D depict cross-sectional images of a Sn-3.8Ag-0.7Cu solder ball after being reflow-soldered to a nickel-gold pad at cooling rates spanning 0.2 to 3.0 °C/sec, in accordance with embodiments of the present invention.

FIGS. 5A-5C depict cross-sectional images of a Sn-3.4Ag-0.9Cu solder ball after being reflow-soldered to a nickel-gold pad at cooling rates spanning 0.2 to 3.0 °C/sec, in accordance

with embodiments of the present invention.

FIGS. 6A-6C depict cross-sectional images of a Sn-3.2Ag-0.9Cu solder ball after being reflow-soldered to a nickel-gold pad at cooling rates spanning 0.2 to 3.0 °C/sec, in accordance with embodiments of the present invention.

FIGS. 7A-7C depict cross-sectional images of a Sn-2.5Ag-0.9Cu solder ball after being reflow-soldered to a nickel-gold pad at cooling rates spanning 0.2 to 3.0 °C/sec, in accordance with embodiments of the present invention.

FIGS. 8A-8C depict cross-sectional images of a Sn-2.1Ag-0.9Cu solder ball after being reflow-soldered to a nickel-gold pad at cooling rates spanning 0.2 to 3.0 °C/sec, in accordance with embodiments of the present invention.

FIGS. 9A-9C depict cross-sectional images of a Sn-3.5Ag solder ball after being reflow-soldered to a nickel-gold pad at cooling rates spanning 0.2 to 3.0 °C/sec, in accordance with embodiments of the present invention.

FIGS. 10A-10C depict cross-sectional images of a Sn-3.5Ag solder ball after being reflow-soldered to a copper pad at cooling rates spanning 0.2 to 3.0 °C/sec, in accordance with embodiments of the present invention.

FIG. 11 is an image of a top view of silver-tin plates of Sn-3.8Ag-0.7Cu solder balls formed on an array of BGA pads wherein the majority tin component of the solder ball has been etched away, in accordance with embodiments of the present invention.

FIG. 12 is a cross-sectional image of a Sn-3.8Ag- 0.7 Cu solder ball joint having silver-tin plates of differing angular orientations, in accordance with embodiments of the present

invention.

FIGS. 13A-3B are images of a silver-tin plate that remained after the majority tin component had been had been etched away from a Sn-3.8Ag-0.7 Cu solder ball, in accordance with embodiments of the present invention.

FIG. 14 is a table showing pasty range variations as a function of copper concentration and silver concentration over a limited compositional range in a Sn-Ag-Cu system, in accordance with embodiments of the present invention.

FIG. 15 is a bar chart showing microhardness as a function of Ag weight percent concentration and cooling rate for a Sn-XAg-0.9Cu SAC alloy wherein X is weight percent silver, in accordance with embodiments of the present invention.

FIG. 16 depicts a section of the ternary Sn-Ag-Cu phase diagram, having a constant Cu concentration of 0.7 wt. %, in accordance with embodiments of the present invention.

Detailed Description of the Invention

FIG. 1A depicts a cross-sectional view of an electrical structure (e.g., an electronic packaging structure) **10**, showing a substrate **12** in position for being soldered to a substrate **18**, in accordance with embodiments of the present invention. An electrically conductive pad ("pad") **13** is attached to the substrate **12**, and a solder ball **14** is coupled to the pad **13**. For example, the solder ball **14** may be in contact with the pad **13** (e.g., in metallurgical and/or electrical contact with the pad **13**). Thus, the substrate **12**, the pad **13**, and the solder ball **14** are coupled together as a single mechanical unit. The solder ball **14** has been coupled to the pad **13** by any method

known to a person of ordinary skill in the art such as, *inter alia*, by reflowing the solder ball **14** onto the pad **13**, followed by cooling and thus solidifying the solder ball **14**. A pad **17** is attached to the substrate **18**, and a solder paste **16** has been applied to the pad **17** and is in contact with the pad **17**. The substrate **12** is to be soldered to the substrate **18** by heating, melting, and reflowing the solder paste **16** and the solder ball **14** such that the melted and reflowed solder from the solder paste **16** is incorporated into the solder ball **14** to form the modified solder ball **15** of FIG. 1B. The modified solder ball **15** comprises the solder paste **16** as having been incorporated into the solder ball **14** during the aforementioned melting and reflowing of the solder paste **16** and the solder ball **14**. After being cooled and solidified, the modified solder ball **15** serves as a solder joint that couples the substrate **12** to the substrate **18**. In some embodiments, the joining of substrates **12** and **18** is performed without the use of the solder paste **16**. In such embodiments, only flux is used to facilitate the joining process. In other embodiments, the solder paste **16** may be used to join substrates **12** and **18**, wherein the solder ball **14** does not melt, but is wetted by the solder paste **16** solder under reflow conditions and provides for attachment upon solidification of the solder paste **16** solder. In FIG. 1A, the electrical structure **10** may be denoted as a "pre-soldering electrical structure."

FIG. 1B depicts a cross-sectional view of the electronic structure **10** of FIG. 1A after the substrate **12** has been soldered to the substrate **18** such that both the solder paste **16** and the solder ball **14** have been fully melted, in accordance with embodiments of the present invention. In FIG. 1B, the solidified modified solder ball **15** serves as a solder joint that couples the substrate **12** to the substrate **18**. The modified solder ball **15** comprises the material of the solder

ball **14** and the material of the solder paste **16** (see FIG. 1A). Generally, N solder balls mechanically and electrically couple the substrate **12** to the substrate **18**, wherein $N \geq 1$, and wherein each of the N solder balls is typified by the modified solder ball **15**. In FIG. 1B, the electrical structure **10** may be denoted as a "post-soldering electrical structure."

In an alternative embodiment, the solder paste **16** is not used and a flux is instead used in accordance with the present invention, using any flux material known to one of ordinary skill in the art, to couple the solder ball **14** to the pad **17**. When the flux is used, the modified solder ball **15** includes essentially the material of the solder ball **14** and does not include any solder paste. In other alternative embodiments, neither flux nor the solder paste **16** is used to couple the solder ball **14** to the pad **17** in accordance with the present invention.

In FIGS. 1A and 1B, the substrates **12** and **18** may each comprise any electrical or electronic composite, laminate, component, etc. As a first example, the substrate **12** may comprise an integrated-circuit chip ("chip") and the substrate **18** may comprise a chip carrier (e.g., a ceramic or organic chip carrier). In chip attachment to a chip carrier, solder paste is typically not used. As a second example, the substrate **12** may comprise a chip carrier (e.g., a ceramic or organic chip carrier) and the substrate **18** may comprise a circuit card. In the second example, the solder ball **14** may be a Ball Grid Array ("BGA") solder ball. The solder pads **13** and **17** may each be any type of solder pad. and comprise any material or materials, known to one of ordinary skill in the art such as, *inter alia*, a copper pad, a nickel-gold plated copper pad ("nickel-gold pad"; i.e., a copper pad coated by a layer of nickel, and a layer of gold coating the layer of nickel), etc. The solder paste **16** may have any applicable composition (e.g., any

applicable substantially lead-free composition) known to a person of ordinary skill in the art. For example, the solder paste **16** may comprise a solder paste composition by weight percent of: 3.5-4.0% silver, 0.5%-0.9% copper, and the remainder as essentially tin with possible additions of small or trace amounts of other constituents. As another example, the solder paste **16** may comprise a solder paste composition by weight percent of: 3.5-4.0% silver and the remainder as essentially tin with possible additions of small or trace amounts of other constituents.

For the present invention, the solder ball **14** comprises an alloy of tin (Sn), silver (Ag), and copper (Cu) having concentrations of Sn, Ag, and Cu ("SAC") that relate to commercial SAC alloy compositions and the ternary eutectic SAC alloy composition. Typically, commercial SAC alloy compositions comprise Sn-3.8Ag-0.7Cu (i.e., 3.8 weight percent Ag and 0.7 weight percent Cu) and Sn-4.0Ag-0.5Cu. Based on the best experimental information in the scientific literature, the ternary eutectic SAC alloy composition is Sn-αAg-βCu, wherein α is about 3.4 to 3.5, and wherein β is between about 0.8 to 0.9. SAC alloy compositions in this near ternary eutectic compositional range are leading lead-free candidate solders to replace the Sn-37Pb alloy that is currently and historically used in electronic component assembly processes.

For notational purposes, whenever the SAC alloy is expressed herein in the form Sn-αAg-βCu, it should be understood that α denotes the weight percent concentration of Ag in the SAC alloy and β denotes the weight percent concentration of Cu in the SAC alloy. The remainder of ($100-\alpha-\beta$) percent of the SAC alloy, by weight, comprises essentially tin and possibly small or trace amounts of other constituents (e.g., bismuth or antimony as will be discussed *infra*). Similar notation with analogous interpretations will be used herein for other alloys than the SAC

alloy, so that a coefficient of a component of an alloy (e.g., the coefficient α or 3.4 of the component Ag of the SAC alloy) denotes the weight percent concentration of the component in the alloy.

As will be demonstrated *infra*, the preceding SAC alloy compositions, when present in the modified solder ball **15** of FIG. 1B, include Ag_3Sn ("silver-tin") plates which may promote fatigue cracking during execution of thermal transients such as during thermal cycle testing simulating field application conditions. The present invention prevents such silver-tin plates from forming, or limits the size of such silver-tin plates, by synergistically exploiting the kinetics in combination with the thermodynamics of phase transformations associated with solidification of the ternary SAC alloy from the liquid state after the SAC alloy has been melted by heating and reflow (melting). The following discussion summarizes aspects of relevant phase transformations that underlie the present invention.

The three phases produced upon full solidification of the liquid SAC alloy (upon cooling from a liquid state) are Sn, Ag_3Sn, and Cu_6Sn_5. For the purposes of this discussion, the ternary eutectic SAC alloy will be used as exemplifying the general behavior of all SAC alloys in this near eutectic compositional range. Upon cooling the liquid phase from temperatures above the melting point, non-equilibrium, kinetic effects intervene to preclude the simultaneous formation of all three phases at the melting point; i.e., to preclude a true eutectic phase transformation, because the equilibrium eutectic phase transformation is kinetically inhibited. The crystalline Ag_3Sn phase is easily nucleated and forms with minimal undercooling (also called "supercooling") below the eutectic melting point of 217 °C of the ternary eutectic SAC alloy.

This Ag_3Sn phase, which is the first solid phase to form upon cooling to and below 217 °C, has a plate-like growth morphology. These plates can grow rapidly in the surrounding liquid phase. The bulk of the liquid phase comprises Sn, and the Sn crystalline phase does not easily nucleate. The crystalline Sn phase requires substantial undercooling for nucleation from the liquid state. Undercoolings of 15 to 25 °C are typically required for the formation of the solid phase of Sn. During the time interval associated with the undercooling required for the nucleation of the crystalline Sn phase, the Ag_3Sn plates can grow to a large size. In processing conditions with typical cooling rates of 0.2 to 0.3 °C/sec, this cooling time interval can comprise tens of seconds and afford sufficient time for the Ag_3Sn plates to grow to a large size. If the nucleation frequency for the Ag_3Sn is low to the extent that only 1 or 2 plates are formed within the modified solder ball **15** of FIG. 1B, then these Ag_3Sn plates can grow large enough to subtend the entire solder joint embodied by the modified solder ball **15**. As will be shown *infra*, these Ag_3Sn plates can adversely affect the thermomechanical fatigue properties of such solder joints, for both chip-to-chip carrier and chip carrier-to-circuit card solder joints. Failure analysis demonstrates that the failures are caused by strain localization at the interface between the Ag_3Sn plates and the bounding solid Sn phase due to grain boundary sliding at this phase boundary. As will be shown *infra*, by altering the Ag concentration within the SAC alloy, the early nucleation and growth of the Ag_3Sn phase can be prevented such that this early fatigue failure mechanism is defeated.

The present invention teaches how to totally, essentially, or substantially suppress formation of the Ag_3Sn plates by either of two methods or by a combination of the two methods. The first method comprises reducing the weight percent concentration of Ag in the SAC alloy to

a value below the eutectic weight percent concentration of Ag such that Ag_3Sn plate formation is thermodynamically impossible until the undercooling required to nucleate the solid Sn phase is reached. The second method comprises cooling the totally liquid phase of the SAC alloy at a cooling rate that is fast enough to prevent any solidified Ag_3Sn from growing to a size that would facilitate fatigue cracking of the modified solder ball **15** of FIG. 1B when the modified solder ball **15** is subject to cyclic or non-cyclic thermal transients (e.g., thermal cycle testing). FIGS. 2-15 provide test support for the preceding two methods. FIG. 16 provides a thermodynamic model that explains the first method and predicts the requisite maximum Ag weight percent concentration that suppresses Ag_3Sn plate formation. Chronologically, the inventors of the present invention first developed the thermodynamic model and used the thermodynamic model to predict the requisite maximum Ag weight percent concentration as a function of undercooling below the eutectic melting temperature of 217 °C of the ternary eutectic SAC alloy. Then the inventors conducted tests that confirmed the predictions of the thermodynamic model. The test results of FIGS. 2-15 are discussed next, followed by a discussion of the thermodynamic model in accordance with FIG. 16.

FIGS. 2A-2B depict cross-sectional images of a solder joint associated with a SAC alloy solder ball **20** after being subject to thermal cycle testing. In FIGS. 2A and 2B, the solder ball **20** is attached to a nickel-gold pad **22** to which a module (i.e., a chip carrier-chip package) had been attached. The solder ball **20** is also attached to a copper pad **24** to which a circuit card had been attached. The pads **22** and **24** each have a 28-mil linear dimension across the pad surface. The solder ball **20** comprised a Sn-3.8Ag-0.7Cu SAC alloy prior to its attachment to the copper pad

24. During attachment of the module to the circuit card, the solder ball **20** was formed with an estimated undercooling of about 15 - 25 °C based on thermocouple measurements using identical circuit card assemblies. The solder joint of solder ball **20** in FIGS. 2A and 2B is one of many similar solder joints, each of which having been subjected to 1000 to 2000 thermal cycles between 0 °C and 100 °C wherein the heating and cooling rates during thermal cycling from 100 °C to 0 °C were about 0.2 °C/sec. The region **26** (shown in FIG. 2A and also in a blown-up view in FIG. 2B) shows localized deformation in the joint structure of the solder ball **20**. The joint structure has a column-like appearance after attachment to both pads **22** and **24**, as shown in FIG. 2A. Because of the coefficient of thermal expansion ("CTE") difference between the module and the card, the solder joint is subject to a cyclic strain within each thermal cycle. After the thermal cycling, some of the solder joints were cross-sectioned to determine the mechanisms for failure. The cross section shown in FIGS. 2A and 2B does not show failure of the joint, but does show localized deformation (i.e., formation of crack **29**) in the region **26** where a Ag_3Sn plate **28** subtends a major fraction of the cross section of the joint. The localized deformation has occurred right at the surface of the plate by initially grain boundary sliding between the silver-tin in the metallic phase and the bounding tin-rich phase. This failure mechanism in some joint structures may lead to early failure such as an electrical open.

FIGS. 3A-3B depict cross-sectional images of a solder joint associated with a ball grid array (BGA) SAC alloy solder ball **30** after being subject to thermal cycle testing. In FIGS. 3A and 3B, the solder ball **30** is attached to a nickel-gold pad **32** to which a module had been attached. The solder ball **30** is also attached to a nickel-gold pad **34** to which a circuit card had

been attached. The pads **32** and **34** each have a 28-mil linear dimension across the pad surface. The solder ball **30** comprised a Sn-3.8Ag-0.7Cu SAC alloy prior to its attachment to the nickel-gold pad **34**. During attachment of the module to the circuit card, the solder ball **30** was formed at a cooling rate of 0.7 - 0.9 °C/sec with an estimated undercooling of about 15 - 25 °C based on thermocouple measurements using identical circuit card assemblies. The solder joint in FIGS. 3A and 3B is one of many similar solder joints, each of which having been subjected to 1500 - 2500 thermal cycles between 0 °C and 100 °C wherein the heating and cooling rates during thermal cycling from 100 °C to 0 °C were about 0.2 °C/sec. The region **36** (shown in FIG. 3A and also in an enlarged view in FIG. 3B) shows localized deformation in the joint structure of the solder ball **30**. A fatigue failure **31** occurred near the pad **32**, and there was no fatigue failure near the pad **34**, which is consistent with the fact that the CTE differential between the solder ball module was much larger than the CTE differential between the solder ball and the circuit card. Near the pad **34**, FIGS. 3A and 3B provide evidence that the Ag_3Sn plate **38** can augment the fatigue cracking initiation process. The Ag_3Sn plate **38** is an intermetallic structure that has grown near the pad **34** from a side of the ball **30**. Due to the fatigue processes, there has been a strain localization at the surface of the Ag_3Sn plate **38** giving rise to a deformation-induced void-like structure **39** at a corner of the pad **34**, and a crack growing from this void-like structure into the bulk of the ball **30**. This shows augmentation of the crack initiation and fatigue processes, which is the primary wearout mechanism for solder joints. The solder joint failure **31** was not caused by the Ag_3Sn plate **38** as discussed *supra*.

FIG. 3C depicts a cross-sectional image of a solder joint associated with a BGA SAC

alloy solder ball **40**, showing crack propagation along a Ag_3Sn plate **48** in the solder ball **40** following thermal cycle testing of the solder joint. In FIG. 3C, the solder ball **40** is attached to a nickel-gold pad **42** to which a module had been attached. The solder ball **40** is also attached to a copper pad **44** to which a circuit card had been attached. The pads **42** and **44** each had a 28-mil linear dimension across the pad surface. The solder ball **40** comprised a Sn-3.8Ag-0.7Cu SAC alloy prior to its attachment to the nickel-gold pad **42**. During attachment of the module to the circuit card, the solder ball **40** was formed at a cooling rate of 0.7 - 0.9 °C/sec with an estimated undercooling of about 15 - 25 °C based on thermocouple measurements using identical circuit card assemblies. The solder joint in FIGS. 3C had been subjected to 2114 thermal cycles between 0 °C and 100 °C wherein the heating and cooling rates during thermal cycling from 100 °C to 0 °C were approximately 0.2 °C/sec. FIG. 3C illustrates propagation of a crack **49** along the surface of the Ag_3Sn plate **48** and continued propagation of the crack **49** through the entire width of solder ball **40** such that the crack **49** constitutes a failure in the form of an electrical open circuit.

In, summary, FIGS. 2A-2B, 3A-3B, and 3C illustrates a correlation between the existence Ag_3Sn plates in SAC alloy solder balls and crack formation and/or fatigue failure in the solder balls following thermal cycling such as, *inter alia*, thermal cycle testing. Thus, it is desirable to prevent or severely inhibit the formation of Ag_3Sn plates in SAC alloy solder balls. FIGS. 4-15 provides testing support for the methods of the present invention for preventing or severely inhibiting the formation of Ag_3Sn plates in SAC alloy solder balls.

FIGS. 4A-4D are cross-sectional images of a SAC alloy solder ball **50** after being reflow-

soldered to a nickel-gold pad **54** at cooling rates of 3.0 °C/sec, 1.2 °C/sec, and 0.2 °C/sec in FIGS. 4A, 4B, and 4C, respectively, in accordance with embodiments of the present invention. FIG. 4D is an enlarged view of the region **56** in FIG. 4C. The solder ball **50** comprised a Sn-3.8Ag-0.7Cu SAC alloy prior to its attachment to the pad **54**. The pad **54** has a 25-mil linear dimension across the pad **54** surface. The peak temperature of the solder ball **50** during a melting reflow process was 240 °C, and the undercooling relative to 217 °C was estimated to be in the range of about 15 - 25 °C for FIGS. 4A - 4D, based on thermocouple measurements using identical or analogous circuit card assemblies. FIGS. 4A an 4B show at most very small Ag_3Sn plates at the 3.0 and 1.2 °C/sec cooling rates, respectively. FIGS. 4C-4D shows Ag_3Sn plates **55, 57, 58,** and **59** wherein the Ag_3Sn plate **57** spans almost the entire length across the solder ball **50**. FIG. 4D also shows a Cu_6Sn_5 structure **53** in the form of a distorted hexagonal rod with round hole in the center of the distorted hexagon. Thus, FIGS. 4A-4D show that Ag_3Sn plates are suppressed or of a very small size in the Sn-3.8Ag-0.7Cu SAC alloy solder ball **50** when the cooling rate is at least 1.2 °C/sec, but is not suppressed and may be large when the cooling rate is 0.2 °C/sec.

Note that the linear length scale on FIGS. 4A-4C is indicated by the "5 mils" text at the upper left corner of each Figure, which denotes that 5 mils of true length corresponds to the length of the line segment directly under the "5 mils" text. Similarly in FIG. 4D, the linear length scale is indicated by the "2 mils" text at the upper left corner of FIG. 4D, which denotes that 2 mils of true length corresponds to the length of the line segment directly under the "2 mils" text. Similar scale indications appear in FIGS. 5-11 and 13, described *infra*.

FIGS. 5A-5C are cross-sectional images of a SAC alloy solder ball **60** after being reflow-

soldered to a nickel-gold pad **64** at cooling rates of 3.0 °C/sec, 1.2 °C/sec, and 0.2 °C/sec in FIGS. 5A, 5B, and 5C, respectively, in accordance with embodiments of the present invention. The solder ball **60** comprised a Sn-3.4Ag-0.9Cu SAC alloy prior to its attachment to the pad **64**. The pad **64** has a 25-mil linear dimension across the pad **64** surface. The undercooling relative to 217 °C was estimated to be in the range of about 15 - 25 °C for FIGS. 5A - 5C, based on thermocouple measurements using identical or analogous circuit card assemblies. FIGS. 5A an 5B show at most very small Ag_3Sn plates at the 3.0 and 1.2 °C/sec cooling rates, respectively. FIG. 5C shows large Ag_3Sn plates **66**, **67**, **68**, and **69**. Thus, FIGS. 5A-5C show that Ag_3Sn plates are suppressed or of a very small size in the Sn-3.4Ag-0.9Cu SAC alloy solder ball **60** when the cooling rate is at least 1.2 °C/sec, but is not suppressed and may be large when the cooling rate is 0.2 °C/sec.

FIGS. 6A-6C are cross-sectional images of a SAC alloy solder ball **70** after being reflow-soldered to a nickel-gold pad **74** at cooling rates of 3.0 °C/sec, 1.2 °C/sec, and 0.2 °C/sec in FIGS. 6A, 6B, and 6C, respectively, in accordance with embodiments of the present invention. The solder ball **70** comprised a Sn-3.2Ag-0.9Cu SAC alloy prior to its attachment to the pad **74**. The pad **74** has a 25-mil linear dimension across the pad **74** surface. The estimated undercooling relative to 217 °C was in the range of about 15 - 25 °C for FIGS. 6A - 6C, based on thermocouple measurements using identical or analogous circuit card assemblies. FIGS. 6A an 6B show at most very small Ag_3Sn plates at the 3.0 and 1.2 °C/sec cooling rates, respectively. FIG. 6C shows large Ag_3Sn plates **76** and **77**. FIG. 6B and 6C shows small Ag_3Sn plates **75**, **78** and **79**, wherein the Ag_3Sn plates **75**, **78** and **79** may be small enough not to facilitate fatigue cracking of

the solder ball **70** when the solder ball **70** is subject to cyclic or non-cyclic thermal transients (e.g., thermal cycle testing). Thus, FIGS. 6A-6C show that Ag_3Sn plates are suppressed or of a very small size in the Sn-3.2Ag-0.9Cu SAC alloy solder ball **70** when the cooling rate is at least 1.2 °C/sec, but is not suppressed and may be large when the cooling rate is 0.2 °C/sec.

FIGS. 7A-7C are cross-sectional images of a SAC alloy solder ball **80** after being reflow-soldered to a nickel-gold pad **84** at cooling rates of 3.0 °C/sec, 1.2 °C/sec, and 0.2 °C/sec in FIGS. 7A, 7B, and 7C, respectively, in accordance with embodiments of the present invention. The solder ball **80** comprised a Sn-2.5Ag-0.9Cu SAC alloy prior to its attachment to the pad **84**. The pad **84** has a 25-mil linear dimension across the pad **84** surface. The estimated undercooling relative to 217 °C was estimated to be in the range of about 15 - 25 °C for FIGS. 7A - 7C, based on thermocouple measurements using identical or analogous circuit card assemblies. FIGS. 7A, 7B, and 7C each show at most very small Ag_3Sn plates at each of the three cooling rates of 3.0, 1.2, and 0.2 °C/sec, respectively. The Ag_3-Sn is solidified not as plates but is dispersed in a striation structure as particulates between the majority tin phase, which shows up in FIGS. 7A-7C as background, light grey striations **82**. The dispersed intermetallic compound structure, comprising Ag_3Sn and Cu_6Sn5 particulates, is quite homogeneous and therefore less susceptible to stress than are the Ag_3Sn plates. Thus, FIGS. 7A-7C show that Ag_3Sn plates are suppressed or of a very small size in the Sn-2.5Ag-0.9Cu SAC alloy solder ball **80** when the cooling rate is in the range of 0.2 to 3.0 °C/sec. Note that essentially the same results of Ag_3Sn plate suppression were obtained for the same test as is shown in FIGS. 7A-7C, except that the Ag concentration was 2.7% instead of 2.5%.

FIGS. 8A-8C are cross-sectional images of a SAC alloy solder ball **90** after being reflow-soldered to a nickel-gold pad **94** at cooling rates of 3.0 °C/sec, 1.2 °C/sec, and 0.2 °C/sec in FIGS. 8A, 8B, and 8C, respectively, in accordance with embodiments of the present invention. The solder ball **90** comprised a Sn-2.1Ag-0.9Cu SAC alloy prior to its attachment to the pad **94**. The pad **94** has a 25-mil linear dimension across the pad **94** surface. The undercooling relative to 217 °C was estimated to be in the range of about 15 - 25 °C for FIGS. 8A - 8C, based on thermocouple measurements using identical or analogous circuit card assemblies. FIGS. 8A, 8B, and 8C each show at most very small Ag_3Sn plates at each of the three cooling rates of 3.0, 1.2, and 0.2 °C/sec, respectively. The Ag_3-Sn is solidified not as plates but is dispersed in a striation structure as has been discussed *supra* in conjunction with FIGS. 7A-7C. Thus, FIGS. 8A-8C show that Ag_3Sn plates are suppressed or of a very small size in the Sn-2.1Ag-0.9Cu SAC alloy solder ball **90** when the cooling rate is in the range of 0.2 to 3.0 °C/sec.

In summary, FIGS. 4-8 show that Ag_3Sn plate formation in a SAC alloy solder ball attached to a substrate (e.g., a circuit card or a chip carrier) is "substantially suppressed" if the Ag concentration in the solder ball is 2.7% or less irrespective of the cooling rate, or if the cooling rate is at least 3.0 °C/sec irrespective of the Ag concentration; and Ag_3Sn plate formation in a SAC alloy solder ball attached to a substrate may not be substantially suppressed if the Ag concentration in the solder ball is 3.2% or more with cooling rates of 1.2 °C/sec or less. Definitionally, Ag_3Sn plate formation in a solder ball (or in a solder joint) is "substantially suppressed" if there is no Ag_3Sn plate formation in the solder ball (or in the solder joint), or if any formed Ag_3Sn plate is small enough so as not to facilitate fatigue cracking of the solder ball

(or solder joint) when the solder ball (or solder joint) is subject to cyclic or non-cyclic thermal induced stresses (e.g., during thermal cycle testing). As an example, the Ag_3Sn plates **75**, **78** and **79** of FIG. 6B and 6C are small enough so as not to facilitate said fatigue cracking, while large Ag_3Sn plates **76** and **77** of FIG. 6C are large enough to facilitate said fatigue cracking. The cutoff Ag concentration below which Ag_3Sn plate formation is substantially suppressed depends on the magnitude of the undercooling as will be explained *infra* in conjunction with the thermodynamic model of FIG. 16. Thus, the cutoff Ag concentration may lie typically somewhere between 2.7% Ag and 3.2% Ag depending on the magnitude of the undercooling. The cutoff Ag concentration can be determined by one of ordinary skill in the art without undue experimentation by performing tests of the type associated with FIGS. 4-8.

Definitionally, Ag_3Sn plate formation in a solder ball (or in a solder joint) is "essentially suppressed" if there is essentially no Ag_3Sn plate formation in the solder ball (or in the solder joint). FIGS. 4-8 show that Ag_3Sn plate formation in a SAC alloy solder ball attached to a substrate (e.g., a circuit card or a chip carrier) is "essentially suppressed" if the Ag concentration in the solder ball is 2.7% or less substantially irrespective of the cooling rate, or if the cooling rate is at least 3.0 °C/sec substantially irrespective of the Ag concentration.

Additionally, FIGS. 4-8 show that Ag_3Sn plate formation in a SAC alloy solder ball attached to a substrate (e.g., a circuit card or a chip carrier) is substantially suppressed, substantially independent of the Ag concentration, if the cooling rate is sufficiently high (i.e., at least about 3.0 °C/sec). Thus, Ag_3Sn plate formation could be substantially suppressed with sufficiently high cooling rates, even if commercial SAC alloy compositions (i.e., 3.8Ag - 4.0 Ag)

or the ternary eutectic SAC alloy composition (i.e., 3.4Ag) is used. Since Ag_3Sn plate formation is not substantially suppressed at a cooling rate of 1.2 °C/sec or less, there is a threshold cooling rate, between 1.2 and 3.0 °C/sec, above which Ag_3Sn plate formation is substantially suppressed. The threshold cooling rate is a function of the composition of the SAC alloy and the available heterogeneous nuclei which foster the nucleation of the solid Sn phase. The threshold cooling rate can be determined by one of ordinary skill in the art without undue experimentation by performing tests of the type associated with FIGS. 4-8.

FIGS. 9A-9C are cross-sectional images of a SAC alloy solder ball **100** after being reflow-soldered to a nickel-gold pad **104** at cooling rates of 3.0 °C/sec, 1.2 °C/sec, and 0.2 °C/sec in FIGS. 9A, 9B, and 9C, respectively, in accordance with embodiments of the present invention. The solder ball **100** comprised a Sn-3.5Ag alloy prior to its attachment to the pad **104**. The pad **104** has a 24-mil linear dimension across the pad **104** surface. The undercooling relative to 217 °C was estimated to be in the range of about 15 - 25 °C for FIGS. 9A - 9C, based on thermocouple measurements using identical or analogous circuit card assemblies. FIGS. 9A, 9B, and 9C each show at most very small Ag_3Sn plates at each of the three cooling rates of 3.0, 1.2, and 0.2 °C/sec, respectively. It is noted that Cu is not a component of the solder ball **100** alloy. Thus, FIGS. 9A-9C show that, even though the Ag concentration by weight is high (i.e., 3.5%), Ag_3Sn plates are substantially suppressed from being formed in the Sn-3.5Ag alloy solder ball **100** (which does not comprise copper) when the cooling rate is in the range of 0.2 to 3.0 °C/sec. This suggests that the absence of copper substantially suppresses large Ag_3Sn plate formation when a solder ball alloy comprising tin and silver (but not copper) is cooled below 217 °C.

FIGS. 10A-10C are cross-sectional images of a SAC alloy solder ball **110** after being reflow-soldered to a copper pad **114** at cooling rates of 3.0 °C/sec, 1.2 °C/sec, and 0.2 °C/sec in FIGS. 10A, 10B, and 10C, respectively, in accordance with embodiments of the present invention. The solder ball **110** comprised a Sn-3.5Ag SAC alloy prior to its attachment to the pad **114**. The pad **114** has a 25-mil linear dimension across the pad **114** surface. The undercooling relative to 217 °C was estimated to be in the range of about 15 - 25 °C for FIGS. 10A - 10C, based on thermocouple measurements using identical or analogous circuit card assemblies. FIGS. 10A and 10B each show at most very small Ag_3Sn plates at each two cooling rates of 3.0 and 1.2 °C/sec, respectively. In contrast, FIG. 10C shows formation of the large Ag_3Sn plate **116** at the cooling rate of 0.2 °C/sec. Although Cu is not a component of the solder ball **110** alloy prior to being heated and reflowed, existence of the Ag_3Sn plate **116** together with the results discussed *supra* for FIGS. 9A-9C suggests that some copper has migrated from the pad **114** into the solder ball **110**. Thus, the combined results shown on FIGS. 10A-10C and 9A-9C suggest that copper may facilitate or augment the nucleation of the Ag_3Sn plates. The inventors of the present invention have also determined that an addition of bismuth similarly facilitates or augments the nucleation of the Ag_3Sn plates. Nonetheless, if the Ag concentration is sufficiently small (i.e., below the cutoff Ag concentration as discussed *supra*), then an addition of bismuth cannot facilitate or augment the nucleation of the Ag_3Sn plates. Note that an addition of bismuth may prevent formation of tin pest as will be discussed *infra*.

FIGS. 11-13 depict the morphology and geometry of Ag_3Sn plates in the SAC solder alloy, in accordance with embodiments of the present invention.

FIG. 11 is an optical image of a top view of Ag_3Sn plates in SAC alloy solder balls attached to an array of BGA pads, wherein the majority Sn component of the SAC alloy has been etched away in FIG. 11 so that only the Ag_3Sn and Cu_6Sn_5 components of the SAC alloy remain on the BGA pads, in accordance with embodiments of the present invention. The SAC alloy solder balls had been formed after being reflow-soldered to nickel-gold pads at a cooling rates of 0.02 °C/sec. The solder balls comprised a Sn-3.8Ag-0.4Cu SAC alloy prior to their being reflow-soldered to the BGA pads. The pads each have a 25-mil linear dimension across the pad surface. The pads appear in FIG. 11 as having approximately circular or slightly elliptical shapes and are organized in an ordered matrix pattern. The Ag_3Sn plates appear in FIG. 11 as plate structures on top of the BGA pads. The largest measured Ag_3Sn plate dimension parallel to the pad surfaces is about 30 mils (i.e., 762 microns). The dimension parallel to the pad surfaces of the distorted hexagonal Cu_6Sn_5 rods is typically about at 0.5 mils (i.e., 13 microns). The Ag_3Sn plate morphology in FIG. 11 is highly variable. Due to the variable Ag_3Sn plate orientation with respect to the viewing direction that is normal to the pad surfaces, some Ag_3Sn plates appear plate-like while other Ag_3Sn plates appear needle-like.

FIG. 12 is a cross-sectional image of a SAC alloy solder ball **120** on a nickel-gold pad **127**, wherein the solder ball **120** comprises Ag_3Sn plates **121-126** with differing angular orientations, in accordance with embodiments of the present invention. The solder ball **120** comprised a Sn-3.8Ag-0.7Cu alloy prior to its attachment to the pad **127**. The angles of the Ag_3Sn plates **121-126** with respect to the direction **129** vary from slightly above zero degrees for the Ag_3Sn plate **124** to slightly below 90 degrees for the Ag_3Sn plate **123**. The SAC alloy solder

ball had been formed after being reflow-soldered to the pad **127** at a cooling rate of 0.02 °C/sec. The undercooling relative to 217 °C was estimated to be in the range of about 15 - 25 °C, based on thermocouple measurements using identical or analogous circuit card assemblies. The pad **127** has a 28-mil linear dimension across the pad **127** surface.

FIGS. 13A-13B are images of an Ag_3Sn plate **130** that remained after the majority Sn component had been had been etched away from a SAC alloy solder ball that had been soldered to a pad, in accordance with embodiments of the present invention. The solder ball **120** comprised a Sn-3.8Ag-0.7Cu alloy prior to its attachment to the pad. The SAC alloy solder ball had been formed after having been subject to a cooling rate of 0.02 °C/sec, after being heated above 217 °C. FIG. 13B is an enlarged view of region **133** of the Ag_3Sn plate **130** of FIG. 13A. FIG. 13B depicts the morphology of the Ag_3Sn plate **130**. The plate **130** was analyzed for its composition using Energy Dispersive X-ray Spectrum (EDS) technology, which confirmed that the plate **130** comprises Ag_3Sn. The plate **130** represents other such plates similarly analyzed as having plate lengths typically in a range of 300-500 microns and plate thicknesses typically in a range of 25-30 microns. A plate length as high as about 800 microns has been observed.

FIG. 14 is a table showing pasty range variations as a function of deviations in copper and silver concentration from a eutectic Sn-3.4Ag-0.7Cu SAC alloy, in accordance with embodiments of the present invention. The pasty range ΔT is the differential between the liquidus temperature ($T_{LIQUIDUS}$) and the solidus temperature ($T_{SOLIDUS}$) for the SAC alloy. FIG. 14 shows ΔT at two copper weight percent concentrations (0.7% and 0.9%) and at five silver weight percent concentrations (2.1%, 2.3%, 2.5%, 2.7%, and 2.9%). FIG. 14 shows ΔT in a 2 - 4 °C

range over the five silver concentrations when the copper concentration is 0.7%, and ΔT in a 16 - 17 °C range over the five silver concentrations when the copper concentration is 0.9%. Thus, ΔT appears to be highly sensitive to the copper concentration but not very sensitive to the silver concentration in this hypoeutectic Ag compositional range

FIG. 14 suggests that if the copper concentration is about 0.7% or lower, then the range over which the SAC alloy melts will be small based on the copper concentration alone, and the copper concentration may enlarge the melting range only by a degree or two. However, if the copper concentration is 0.9% or higher, then the two-phase temperature window over which solidification/melting occurs is much larger (e.g., at least 15 °C), which may be unacceptable because the solder defect rate in the solder joint could go up dramatically. Such solder defects include, *inter alia*, fillet lifting, pad lifting, solder ball lifting, etc., all of which may cause an open-circuit in the solder joint. Thus, depending on how significant the pasty range is in an intended application, it is may be desirable for the copper concentration in the SAC solder ball to be no higher than 0.7, 0.8, 0.9 weight percent. Generally, the pasty range can be controlled by the copper weight percent concentration in the SAC alloy in a manner that reflects the intended application. Thus, depending on the application, the pasty range may be controlled so as to be no more than a value such as 1 °C, 3 °C, 5 °C, 10 °C, 15 °C, 25 °C, etc.

The preceding FIG. 14 results may be applied to the effect of soldering a SAC solder ball to either a copper pad or a nickel gold pad for the case in which the initial Cu concentration in the solder ball (i.e., the Cu concentration prior to reflow) is about 0.7%. If the pad is a copper pad, then during heating and reflow, copper in the pad migrates to the liquid solder ball which

could raise the Cu concentration in the solder ball to 1.0% in just two or three reflows. At each successive reflow, the copper concentration in the solder ball increases until the copper concentration in the liquid tin reaches saturation. If more copper were added when the copper concentration is at the saturated copper concentration, the excess copper would come out of solution as a Cu_6Sn_5 precipitant. The saturated copper concentration is temperature dependent and is about 1.5% at about 250 °C. One could, of course, start with a SAC solder ball having a copper concentration of 1.5% prior to the solder ball being solder reflowed to a copper pad.

If it is desired to prevent the SAC solder ball from having a final Cu concentration (i.e., an after-reflow Cu concentration) of no more than about 0.7%, the initial Cu concentration in the solder ball may be set to no more than about 0.4 or 0.5 %. These considerations also apply to other solderable surface finishes such as immersion Ag and Pd surface finishes having thin surface plating. In these instances, the thin surface plating is readily dissolved in the solder during a single reflow. Under these conditions, the underlying Cu pad is typically exposed to the solder and the Cu concentration in the solder joint can rise, accordingly. If the pad is a nickel-gold pad, however then during heating and reflow, the nickel in the intermetallic phase at the pad interface ties up a substantial portion of the total fraction of the initial copper in the solder ball, causing the copper concentration of the solder ball to drop. Thus if the initial Cu concentration is about 0.7% and if the SAC solder ball is soldered to a nickel-gold pad, then the copper concentration of the SAC solder ball could be reduced to 0.4% in just 2 or 3 reflows. Thus, there is a wide range of copper that is comprised by the after-reflow solder ball depending on the pad material to which the solder ball has been soldered. However, lowering the Cu concentration is

not adverse from a pasty range point of view, as explained *supra*, and it may therefore desirable for the after-reflow Cu concentration in the solder ball to be at or below the eutectic Cu concentration of about 0.7% so that the pasty range is reasonably bounded to no more than about two or three °C. Accordingly, if the same solder ball alloy concentrations are used for both types of pads (i.e., a copper pad or a nickel-gold pad), then the initial copper concentration may be about 0.5 or 0.6%, so that the final copper concentration would end up at about 0.2% for a nickel-gold pad and at about 0.7 % for a copper pad, depending on the number of reflow cycles.

Generally, there is no requirement for a lower bound of copper concentration in the SAC alloy. Nonetheless, the melting temperature of the eutectic tin-silver alloy is 221 °C, and as copper is added to the eutectic tin-silver alloy the melting temperature decreases monotonically as the cooper wight percent increases such that the melting temperature is reduced to about 217 °C as the copper weight percent concentration is increased to the 0.7% - 0.9% range. Since having a lower melting temperature for copper may be significant for some applications, it may be desirable for some applications for the copper weight percent concentration concentration to be at least about Y%, wherein representative values of Y% are 0.1%, 0.2%, 0.3%, 0.4%, 0.5%, 0.6%, and 0.7%.

In utilizing the present invention, the solder paste composition may be taken into account. For example, a commercial solder paste having 4.0Ag is in widespread use currently. If a purchaser of the SAC solder ball utilizes the 4.0Ag solder paste with a SAC solder ball of the present invention, the SAC solder ball Ag concentration may be adjusted downward to compensate for the additive Ag effect of the solder paste by 0.2%, and another 0.2% based on a

tolerance used by manufacturers of the SAC solder ball. Thus, if 2.7Ag or 2.8Ag is the maximum desirable Ag concentration of the solder joint associated with the solder ball, then the initial Ag concentration of the solder ball may be reduced by 0.4% to account for both the solder paste composition and the solder ball manufacturer's compositional tolerance. Accordingly, the manufacturer would produce modules with a solder ball Ag concentration close to 2.3%. Note that the preceding numbers are merely illustrative, since the Ag concentration in the solder paste may vary and the manufacturer's solder ball tolerance may vary. Generally, the initial Ag concentration of the solder ball may be additively reduced by both the effect of the Ag concentration of the solder paste and the solder ball manufacturer's compositional tolerance. Thus, in many embodiments the Ag concentration of the solder joint exceeds the initial Ag concentration of the solder ball by at least about 0.2% (e.g., by 0.4% in the preceding example). Also note that if the Ag concentration of the solder paste is less than the desired Ag concentration of the SAC solder ball , then the effect of the solder paste on adjusting the initial Ag concentration of the SAC solder ball would be subtractive rather than additive.

Another aspect of the present invention involves adding at least 0.1% bismuth (Bi) (e.g., 0.1% to 0.2% bismuth) to the SAC solder ball to prevent tin pest from occurring. Tin pest may occur at a temperature well below room temperature and is characterized by an allotropic phase transformation of tin which transforms the normal tetragonal structure of tin ("white tin") into a body-centered cubic structure of tin(i.e., a "grey tin" powder). The transformation from white tin to grey tin destroys the mechanical properties of the structure that comprises the tin. The bismuth additive will suppress tin pest. Another additive that will suppress tin pest is antimony

(Sb). However, bismuth is less toxic than antimony under some conditions associated with recycling of electronic assembly materials. Nonetheless, either bismuth or antimony may be added to the SAC solder ball of the present invention. Higher levels of bismuth and antimony may, in some instances, be added to improve solder wetting and/or the mechanical properties of the solder joints. Additionally, any additive that is known to a person of ordinary skill in the art as useful for suppressing tin pest may be added to the SAC solder ball of the present invention.

FIG. 15 is a bar chart resulting from microhardness tests conducted at a Vicker's force level of 10 grams. FIG. 15 shows microhardness as a function of Ag weight percent concentration and cooling rate for a Sn-XAg-0.9Cu SAC alloy wherein X is weight percent silver, in accordance with embodiments of the present invention. Note that with respect to having higher thermal cycle fatigue life, relatively lower values of microhardness are more desirable than relatively higher values of microhardness. In FIG. 15, the lighter bars denote a SAC alloy tested for microhardness after having been formed at a cooling rate of 0.02 °C/sec. The black bars denote a SAC alloy tested for microhardness as received from the SAC alloy vendor and said as-received SAC alloy had been formed at a very rapid cooling rate (i.e., much more rapid than 0.02 °C/sec). Let ΔH denote a differential in hardness between the as-received alloy and the 0.02 °C/sec cooled alloy, at a given value Z of silver concentration in weight percent FIG. 15 shows much larger values of ΔH at the highest value of Z (i.e., at 3.0Ag - 3.4Ag) than at the lowest values of Z (i.e., at 2.0Ag - 2.5Ag). At 2.0Ag - 2.5Ag, ΔH is only 2 to 3 Hv. The relatively large values of ΔH at 3.0Ag - 3.4Ag (i.e., 4 to 8 Hv) are likely caused by the presence of Ag_3Sn plates in the slowly cooled condition and the absence of large plates in the

rapidly cooled condition. In both types of solidified structures, the same amount of Ag_3Sn exits; however, the Ag_3Sn is dispersed differently in the two solidified structures leading to the hardness variation. The Ag_3Sn incorporated in the large plates takes away material that can later be incorporated in the Sn matrix as finely dispersed Ag_3Sn particulates upon final solidification. The dispersed fine particulates of Ag_3Sn are arrayed in dense web like patterns between the Sn dendritic structures. These structures are distributed evenly across the solder joint. However, the density of these structures increases as the Ag concentration in the liquid phase which undergoes the final solidification (producing the solid Sn phase) increases. These more dense structures manifest higher hardnesses. The relatively small values of ΔH at 2.0Ag - 2.5Ag (where Ag_3Sn plate formation is suppressed in accordance with the present invention) is desirable, since the microhardness is insensitive to the processing conditions that are used to assemble a SAC solder ball to a circuit card.

FIG. 16 depicts a section (i.e., a cut) at a constant Cu concentration of 0.7 wt. % of the ternary Sn-Ag-Cu phase diagram, in accordance with embodiments of the present invention. In the pure liquid region **210**, which is located to the left of the liquidus line **200** as shown, Ag_3Sn cannot exist in equilibrium; i.e., Ag_3Sn cannot nucleate and grow. If Ag_3Sn were present in the pure liquid region **210**, then the Ag_3Sn would dissolve back into the pure liquid of region **210**. In region **220**, which is located to the right of the liquidus line **200** as shown, Ag_3Sn can nucleate and grow; Ag_3Sn plates can therefore exist in region **220**. The region **230** lies below the eutectic melting line **217** of 217 °C. In the region **230**, the Sn liquid phase is substantially metastable and cannot easily nucleate. Independent measurements by the inventors of the solidification process

in the Sn-3.8Ag-0.7 Cu alloy, using differential scanning calorimetry at scan rates of 0.1 °C /sec, have shown undercoolings of 15 °C to 30 °C before the Sn phase solidifies. The metastability of the liquid Sn phase depends on the availability of sites for heterogeneous nucleation to take place.

Extrapolated line **201** represents an extrapolation of the liquidus line **200** below the eutectic melting line **217** into the metastable region **230**. The extrapolated line **201** is nonlinear and is formed by extrapolation that takes the curvature of the liquidus line **200** into account. The region **230** has two portions: a portion **231** to the left of the extrapolated line **201**, and a portion **232** to the right of the extrapolated line **201**. A ternary phase transformation under equilibrium conditions would require essentially no undercooling and would enable solidification (i.e., crystallization) of all three phases (i.e., the Sn, Ag_3Sn, and Cu_6Sn_5 phases) at 217 °C. With the ternary system in FIG. 16, there is no ternary phase transformation, because the tin phase is not easily nucleated, but rather is easily supercooled (i.e., undercooled) in the liquid state and is thus metastable substantially below the line **217** of 217 °C. The extrapolated line **201** has the thermodynamic characteristics of the liquidus line **200** under this metastable condition. Therefore, in the portion **231** of the region **230**, Ag_3Sn cannot exist in equilibrium and thus cannot nucleate and grow. Accordingly, if a given amount of undercooling (δT) below the line **217** is assumed, then the extrapolated line **201** may be used to infer the maximum Ag weight percent (Ag_{MAX}) that will place the ternary mixture in the portion **231** of the region **230**. Thus if the Ag weight percent is Ag_{MAX} and the temperature is at least 217 °C - δT, then solidified Ag_3Sn is thermodynamically barred from being formed, because the ternary composition is in the

portion **231** of the region **230**. As a first example, if δT=10 °C then Ag_{MAX}=3.0%, from use of the extrapolated line **201**. As a second example, if δT=20 °C then Ag_{MAX}=2.7%, from use of the extrapolated line **201**. As a third example, if δT=30 °C then Ag_{MAX}=2.5%, from use of the extrapolated line **201**. The preceding values of Ag_{MAX} were not determined graphically from FIG. 16, but were determined numerically by using the nonlinear equation that represents the extrapolated line **201**. Thus if the temperature is at least 207 °C, 197 °C, or 187 °C, then the Ag_3Sn cannot nucleate if the Ag weight percent is no higher than 3.0%, 2.7%, or 2.5%, respectively. The preceding model uses as a temperature baseline the eutectic temperature of 217 °C at which tin would nucleate under equilibrium conditions. The tin phase in the region **230** below 217 °C is undercooled and would nucleate if it could, but it cannot because such nucleation is kinetically inhibited. However, with sufficient undercooling δT, the tin phase will nucleate. Typically, such sufficient undercooling δT is about 15 -25 °C based on experimental data to which the inventors have access. Thus if the tin begins to nucleate at 217 °C minus 15 °C, then based on the preceding calculations, the Ag concentration in the alloy should be no more than 2.8-2.9% so that the Ag_3Sn cannot begin to nucleate until the temperature is 15 °C below 217 °C. Similarly, if the tin begins to nucleate at 217 °C minus 25 °C, then based on the preceding calculations, the Ag concentration should be no more than 2.6% so that the Ag_3Sn cannot begin to nucleate until the temperature is 25 °C below 217 °C. Accordingly, the maximum Ag concentration to thermodynamically prevent nucleation of Ag_3Sn is 2.6% if δT=25 °C and 2.8-2.9% if δT=15 °C. Although nucleation and growth are kinetic phenomena, the present invention thermodynamically bars the nucleation and growth from occurring, because

incipient nuclei are thermodynamically unstable if the ternary composition is confined to the portion **231** of the region **230**.

In relation to the preceding discussion of FIG. 16, let the silver have a weight percent concentration X in the SAC alloy. In accordance with the present invention, X is sufficiently small (such as, *inter alia*, by selection or by predetermination) that formation of Ag_3Sn plates is substantially suppressed when the SAC alloy in a liquefied state is being solidified by being cooled to a lower temperature T_L at which the solid Sn phase is nucleated. The lower temperature T_L corresponds to the undercooling δT relative to the eutectic melting temperature T_E of the SAC alloy, wherein T_E is about equal to 217 °C. Mathematically, this means that $T_L = T_E - \delta T$.

In consideration of the magnitudes and variations in weight percent concentration of silver and copper in the SAC alloy as well as small amounts of other alloy constituents such as bismuth that may be present, as discussed *supra* for the present invention, the majority constituent of tin in the SAC alloy of the present invention is at least about 90%.

While embodiments of the present invention have been described herein for purposes of illustration, many modifications and changes will become apparent to those skilled in the art. Accordingly, the appended claims are intended to encompass all such modifications and changes as fall within the true spirit and scope of this invention.

Claims

What is claimed is:

1. A solder composition, comprising a solder alloy,

wherein the alloy is substantially free of lead,

wherein the alloy includes tin (Sn), silver (Ag), and copper (Cu),

wherein the tin has a weight percent concentration in the alloy of at least about 90%,

wherein the silver has a weight percent concentration of X in the alloy,

wherein X is sufficiently small that formation of Ag_3Sn plates is substantially suppressed when the alloy in a liquefied state is being solidified by being cooled at to a lower temperature at which the solid Sn phase is nucleated,

wherein the lower temperature corresponds to an undercooling δT relative to the eutectic melting temperature of the alloy, and

wherein the copper has a weight percent concentration in the alloy not exceeding about 1.5%.

2. The composition of claim 1, wherein X has a predetermined value based on X being sufficiently small that formation of said Ag_3Sn plates is substantially suppressed during said cooling of said alloy in said liquefied state.

3. The composition of claim 1, wherein X does not exceed X_{MAX}, and wherein X_{MAX} is the maximum silver weight percent concentration in the liquefied alloy at which Ag_3Sn plates are thermodynamically barred from being formed in the liquefied alloy during said cooling of the liquefied alloy.

4. The composition of claim 3, wherein X_{MAX} is a function of δT, said function being derived from a ternary phase diagram and associated thermodynamic data relating to a ternary mixture of Sn, Ag, and Cu.

5. The composition of claim 1, wherein the copper weight percent concentration in the liquefied alloy is sufficiently small that the pasty range of the liquefied alloy does not exceed about 10 °C.

6. The composition of claim 1, wherein the copper weight percent concentration in the liquefied alloy does not exceed about 0.9%.

7. The composition of claim 1, wherein the alloy further includes a substance that suppresses tin pest formation in the solidified alloy.

8. The composition of claim 7, wherein the substance comprises bismuth, and wherein the bismuth has a weight percent concentration of at least 0.1%. in the alloy.

9. The composition of claim 1, wherein X does not exceed about 2.8%.

10. The composition of claim 1, wherein X is in a range of about 2.6% to about 2.8%.

11. A method for forming an electrical structure, comprising:

providing a first substrate and a first solder ball attached to a first electrically conductive pad that is coupled to the first substrate, wherein the first solder ball comprises a solder alloy, wherein the alloy is substantially free of lead, wherein the alloy includes tin (Sn), silver (Ag), and copper (Cu), wherein the tin has a weight percent concentration in the alloy of at least about 90%, and wherein the copper has a weight percent concentration in the alloy not exceeding about 1.5%;

providing a second substrate and a second electrically conductive pad coupled to the second substrate;

coupling the first solder ball to the second pad;

melting the first solder ball by heating the first solder ball to form a modified solder ball; and

solidifying the modified solder ball by cooling the modified solder ball to a lower temperature at which the solid Sn phase is nucleated, and wherein the lower temperature corresponds to an undercooling δT relative to the eutectic melting temperature of the alloy, wherein the solidified modified solder ball is a solder joint that couples the first substrate to the second substrate, and wherein a silver weight percent concentration X_2 in the modified solder ball is sufficiently small that formation of Ag_3Sn plates is substantially suppressed during said cooling.

12. The method of claim 11, wherein providing the first substrate and the first solder ball comprises selecting a silver weight percent concentration X_1 in the alloy of the first solder ball such that X_2 is sufficiently small that said formation of the Ag_3Sn plates is substantially suppressed during said cooling.

13. The method of claim 11, wherein X_2 does not exceed X_{MAX}, wherein X_{MAX} is the maximum silver weight percent concentration in the modified solder ball at which Ag_3Sn plates are thermodynamically barred from being formed in the modified solder ball during said cooling.

14. The method of claim 13, further comprising determining X_{MAX} as a function of δT from a ternary phase diagram and associated thermodynamic data relating to a ternary mixture of Sn, Ag, and Cu.

15. The method of claim 11, wherein the first substrate comprises a chip carrier, and wherein the second substrate comprises a circuit card.

16. The method of claim 15, wherein the first solder ball is a ball grid array (BGA) solder ball.

17. The method of claim 11, wherein the first substrate comprises a chip, and wherein the second substrate comprises a chip carrier.

18. The method of claim 11, wherein X_2 is in a range of about 2.6% to about 2.8%.

19. The method of claim 11, wherein X_2 does not exceed about 2.8%.

20. The method of claim 11, wherein the copper weight percent concentration in the modified solder ball during cooling is sufficiently small that the pasty range of the modified solder ball during cooling does not exceed about 10 °C.

21. The method of claim 11, wherein the copper weight percent concentration in the modified solder ball does not exceed about 0.9%.

22. The method of claim 11, wherein the second pad is a copper pad.

23. The method of claim 11, wherein the second pad is a copper pad, and wherein the copper weight percent concentration in the first solder ball does not exceed about 0.5%.

24. The method of claim 11, wherein the second pad is a nickel-gold pad.

25. The method of claim 11, wherein the alloy further includes a substance that suppresses tin pest formation in the alloy.

26. The method of claim 11, wherein coupling the first solder ball to the second pad comprises applying a flux to the second pad and placing the first solder ball in contact with the flux.

27. The method of claim 11,

wherein coupling the first solder ball to the second pad comprises applying a solder paste to the second pad and placing the first solder ball in contact with the solder paste, and

wherein melting the first solder ball comprises melting the first solder ball and the solder paste by heating the first solder ball and the solder paste, such that the melted solder paste is incorporated into the melted first solder ball to form the modified solder ball, and such that the modified solder ball includes the solder paste within the first solder ball.

28. The method of claim 27, wherein the solder paste includes a weight percent silver X_P that exceeds the silver weight percent concentration X_1 in the alloy of the first solder ball, and wherein $X_2 - X_1$ is at least 0.2%.

29. A method for forming a solder composition, comprising:

providing a solder alloy, wherein the alloy is substantially free of lead, wherein the alloy includes tin (Sn), silver (Ag), and copper (Cu), wherein the tin has a weight percent concentration in the alloy of at least about 90%, wherein the silver has a weight percent concentration in the alloy not exceeding about 4.0%, and wherein the copper has a weight percent concentration in the alloy not exceeding about 1.5%;

melting the alloy by heating the alloy; and

solidifying the melted alloy by cooling the melted alloy at a cooling rate that is high enough to substantially suppress Ag_3Sn plate formation in the alloy during said cooling.

30. The method of claim 29, further comprising, prior to said solidifying, selecting the cooling rate that is high enough to substantially suppress said Ag_3Sn plate formation in the alloy.

31. The method of claim 29, wherein the cooling rate is at least about 1.2 °C/sec.

32. The method of claim 29, wherein the copper weight percent concentration in the melted alloy is sufficiently small that the pasty range of the melted alloy does not exceed about 10 °C.

33. The method of claim 29, wherein the copper weight percent concentration in the melted alloy does not exceed about 0.9%.

34. The method of claim 29, wherein the alloy further includes a substance that suppresses tin pest formation in the solidified alloy.

35. The method of claim 34, wherein the substance comprises bismuth, and wherein the bismuth has a weight percent concentration of at least 0.1% in the alloy.

36. A method for forming an electrical structure, comprising:

providing a first substrate and a first solder ball attached to a first electrically conductive pad that is coupled to the first substrate, wherein the first solder ball comprises a solder alloy, wherein the alloy is substantially free of lead, wherein the alloy includes tin (Sn), silver (Ag), and copper (Cu), wherein the tin has a weight percent concentration in the alloy of at least about 90%, wherein the silver has a weight percent concentration in the alloy not exceeding about 4.0%, and wherein the copper has a weight percent concentration in the alloy not exceeding about 1.5%;

providing a second substrate and a second electrically conductive pad coupled to the second substrate;

coupling the first solder ball to the second pad;

melting the first solder ball by heating the first solder ball to form a modified solder ball; and

solidifying the modified solder ball by cooling the modified solder ball at a cooling rate that is high enough to substantially suppress Ag_3Sn plate formation in the modified solder ball during said cooling, wherein the solidified modified solder ball is a solder joint that couples the first substrate to the second substrate.

37. The method of claim 36, further comprising, prior to said solidifying, selecting the cooling rate that is high enough to substantially suppress said Ag_3Sn plate formation in the modified solder ball.

38. The method of claim 36, wherein the first substrate comprises a chip carrier, and wherein the second substrate comprises a circuit card.

39. The method of claim 38, wherein the first solder ball is a ball grid array (BGA) solder ball.

40. The method of claim 36, wherein the first substrate comprises a chip, and wherein the second substrate comprises a chip carrier.

41. The method of claim 36, wherein the cooling rate is at least about 1.2 °C/sec.

42. The method of claim 36, wherein the copper weight percent concentration in the alloy is sufficiently small that the pasty range of the alloy does not exceed about 10 °C.

43. The method of claim 36, wherein the copper weight percent concentration in the alloy does not exceed about 0.9%.

44. The method of claim 36, wherein the second pad is a copper pad.

45. The method of claim 36, wherein the second pad is a copper pad, and wherein the copper weight percent concentration in the first solder ball does not exceed about 0.5%.

46. The method of claim 36, wherein the second pad is a nickel-gold pad.

47. The method of claim 36, wherein the alloy further includes a substance that suppresses tin pest formation in the alloy.

48. The method of claim 36, wherein coupling the first solder ball to the second pad comprises applying a flux to the second pad and placing the first solder ball in contact with the flux.

49. The method of claim 36,

wherein coupling the first solder ball to the second pad comprises applying a solder paste to the second pad and placing the first solder ball in contact with the solder paste, and

wherein melting the first solder ball comprises melting the first solder ball and the solder paste by heating the first solder ball and the solder paste, such that the melted solder paste is incorporated into the melted first solder ball to form the modified solder ball, and such that the modified solder ball includes the solder paste within the first solder ball.

50. A pre-soldering electrical structure, comprising:

a first substrate and a first solder ball attached to a first electrically conductive pad that is coupled to the first substrate, wherein the first solder ball comprises a solder alloy, wherein the alloy is substantially free of lead, wherein the alloy includes tin (Sn), silver (Ag), and copper (Cu), wherein the tin has a weight percent concentration in the alloy of at least about 90%, and wherein the copper has a weight percent concentration in the alloy not exceeding about 1.5%;

a second substrate and a second electrically conductive pad coupled to the second substrate, wherein the first solder ball is coupled to the second pad, wherein the first solder ball is adapted to being melted by being heated to form a modified solder ball, wherein the modified solder ball is adapted to being solidified by being cooled to a lower temperature at which the solid Sn phase is nucleated, wherein the lower temperature corresponds to an undercooling δT relative to the eutectic melting temperature of the alloy, wherein the solidified modified solder ball is a solder joint that couples the first substrate to the second substrate, and wherein a silver weight percent concentration X_2 in the modified solder ball is sufficiently small that formation of Ag_3Sn plates are substantially suppressed during said cooling.

51. The electrical structure of claim 50, wherein the alloy of the first solder ball has a silver weight percent concentration X_1, and wherein X_1 has a predetermined value based on X_2 being sufficiently small that formation of said Ag_3Sn plates is substantially suppressed during cooling of said modified solder ball.

52. The electrical structure of claim 50, wherein X_2 does not exceed X_{MAX}, wherein X_{MAX} is the maximum silver weight percent concentration in the modified solder ball at which Ag_3Sn plates are thermodynamically barred from being formed in the modified solder ball during said cooling.

53. The electrical structure of claim 52, wherein X_{MAX} is a function of δT, said function being derived from a ternary phase diagram and associated thermodynamic data relating to a ternary mixture of Sn, Ag, and Cu.

54. The electrical structure of claim 50, wherein the first substrate comprises a chip carrier, and wherein the second substrate comprises a circuit card.

55. The electrical structure of claim 54, wherein the first solder ball is a ball grid array (BGA) solder ball.

56. The electrical structure of claim 50, wherein the first substrate comprises a chip, and wherein the second substrate comprises a chip carrier.

57. The electrical structure of claim 50, wherein X_2 is in a range of about 2.6% to about 2.8%.

58. The electrical structure of claim 50, wherein X_2 does not exceed about 2.8%.

59. The electrical structure of claim 50, wherein the solder paste includes a weight percent silver X_P that exceeds X_1, wherein X_1 is the weight percent silver in the first solder ball, and wherein $X_2 - X_1$ is at least 0.2%.

60. The electrical structure of claim 50, wherein the copper weight percent concentration in the modified solder ball during cooling is sufficiently small that the pasty range of the modified solder ball during cooling does not exceed about 10 °C.

61. The electrical structure of claim 50, wherein the copper weight percent concentration in the modified solder ball does not exceed about 0.9%.

62. The electrical structure of claim 50, wherein the second pad is a copper pad.

63. The electrical structure of claim 62, wherein the second pad is a copper pad, and wherein the copper weight percent concentration in the first solder ball does not exceed about 0.5%.

64. The electrical structure of claim 50, wherein the second pad is a nickel-gold pad.

65. The electrical structure of claim 50, wherein the alloy further includes a substance that suppresses tin pest formation in the modified solder ball.

66. The electrical structure of claim 65, wherein the substance comprises bismuth, and wherein the bismuth has a weight percent concentration of at least 0.1%. in the alloy.

67. The electrical structure of claim 50, wherein the first solder ball is coupled to the second pad by a flux that is applied to the second pad such that the first solder ball in contact with the flux.

68. The electrical structure of claim 50,

wherein the first solder ball is coupled to the second pad by a solder paste that is applied to the second pad such that the first solder ball in contact with the solder paste; and

wherein the first solder ball is adapted to being melted by heating the first solder ball and the solder paste, such that the melted solder paste is incorporated into the melted first solder ball to form the modified solder ball, and such that the modified solder ball includes the solder paste within the first solder ball.

69. A post-soldering electrical structure comprising:

a first substrate; and

a second substrate, wherein the first substrate is coupled to the second substrate by a solder joint, wherein the solder joint comprises an alloy, wherein the alloy is substantially free of lead, wherein the alloy includes tin (Sn), silver (Ag), and copper (Cu), wherein the tin has a weight percent concentration in the alloy of at least about 90%, wherein the silver has a weight percent concentration in the alloy of X_2, wherein X_2 is sufficiently small that Ag_3Sn plates are substantially absent in the solder joint, and wherein the copper has a weight percent concentration in the alloy not exceeding about 1.5%.

70. The electrical structure of claim 69, wherein the solder joint is formed from a first solder ball having a tin-silver-copper composition in which the silver has a weight percent concentration X_1, wherein X_1 has a predetermined value based on X_2 being sufficiently small that said Ag_3Sn plates are substantially absent in the solder joint.

71. The electrical structure of claim 69, wherein the first substrate comprises a chip carrier, and wherein the second substrate comprises a circuit card.

72. The electrical structure of claim 71 wherein the solder joint includes a ball grid array (BGA) solder ball.

73. The electrical structure of claim 69, wherein the first substrate comprises a chip, and wherein the second substrate comprises a chip carrier.

74. The electrical structure of claim 69, wherein X_2 is in a range of about 2.6% to about 2.8%.

75. The electrical structure of claim 69, wherein X_2 does not exceed about 2.8%.

76. The electrical structure of claim 69, wherein the copper weight percent concentration in the solder joint is sufficiently small that the pasty range of the solder joint does not exceed about 10 °C.

77. The electrical structure of claim 69, wherein the copper weight percent concentration in the solder joint does not exceed about 0.9%.

78. The electrical structure of claim 69, wherein the alloy further includes a substance that suppresses tin pest formation in the alloy.

79. The electrical structure of claim 78, wherein the substance comprises bismuth, and wherein the bismuth has a weight percent concentration of at least 0.1%. in the alloy.

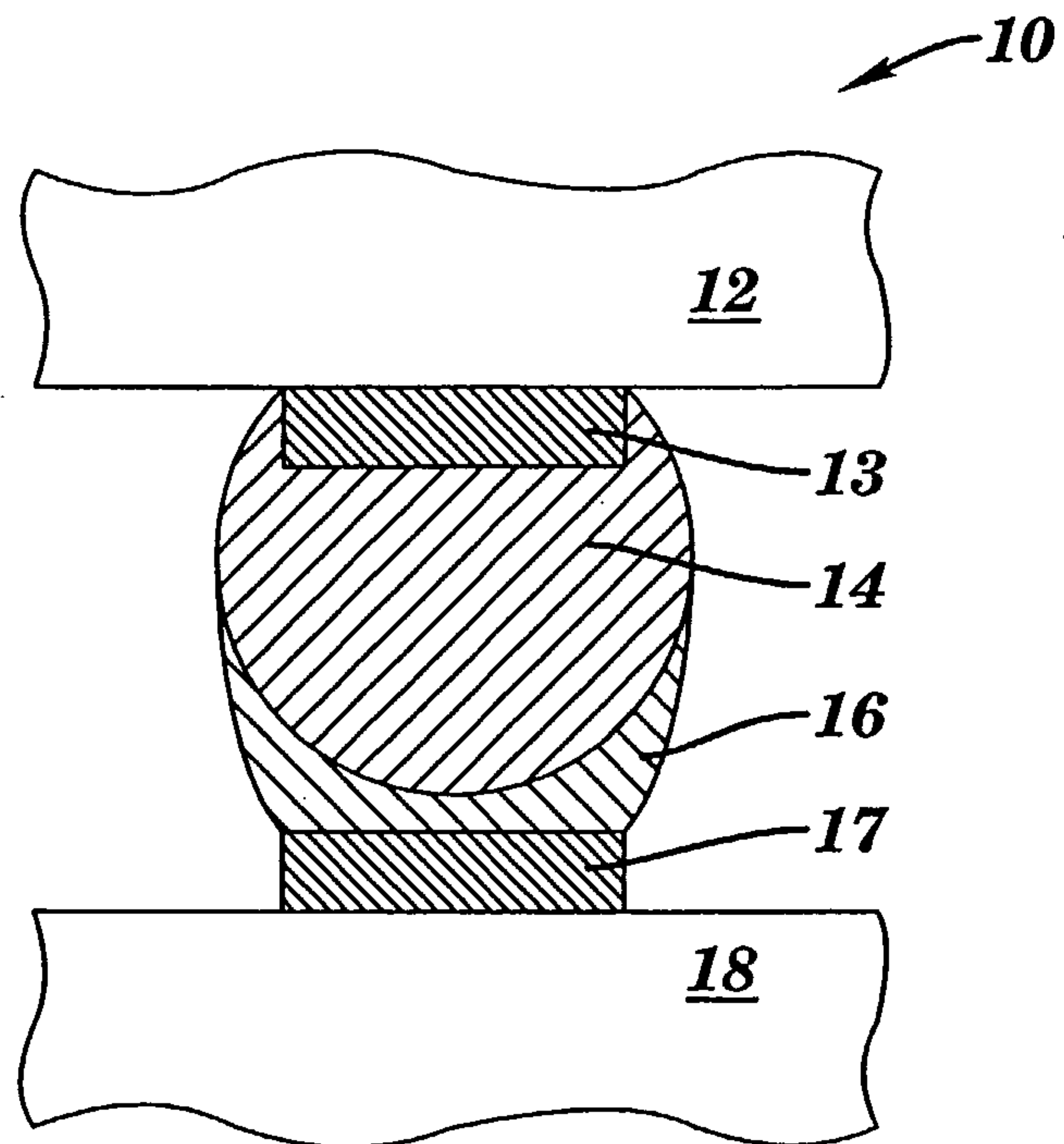

FIG. 1A

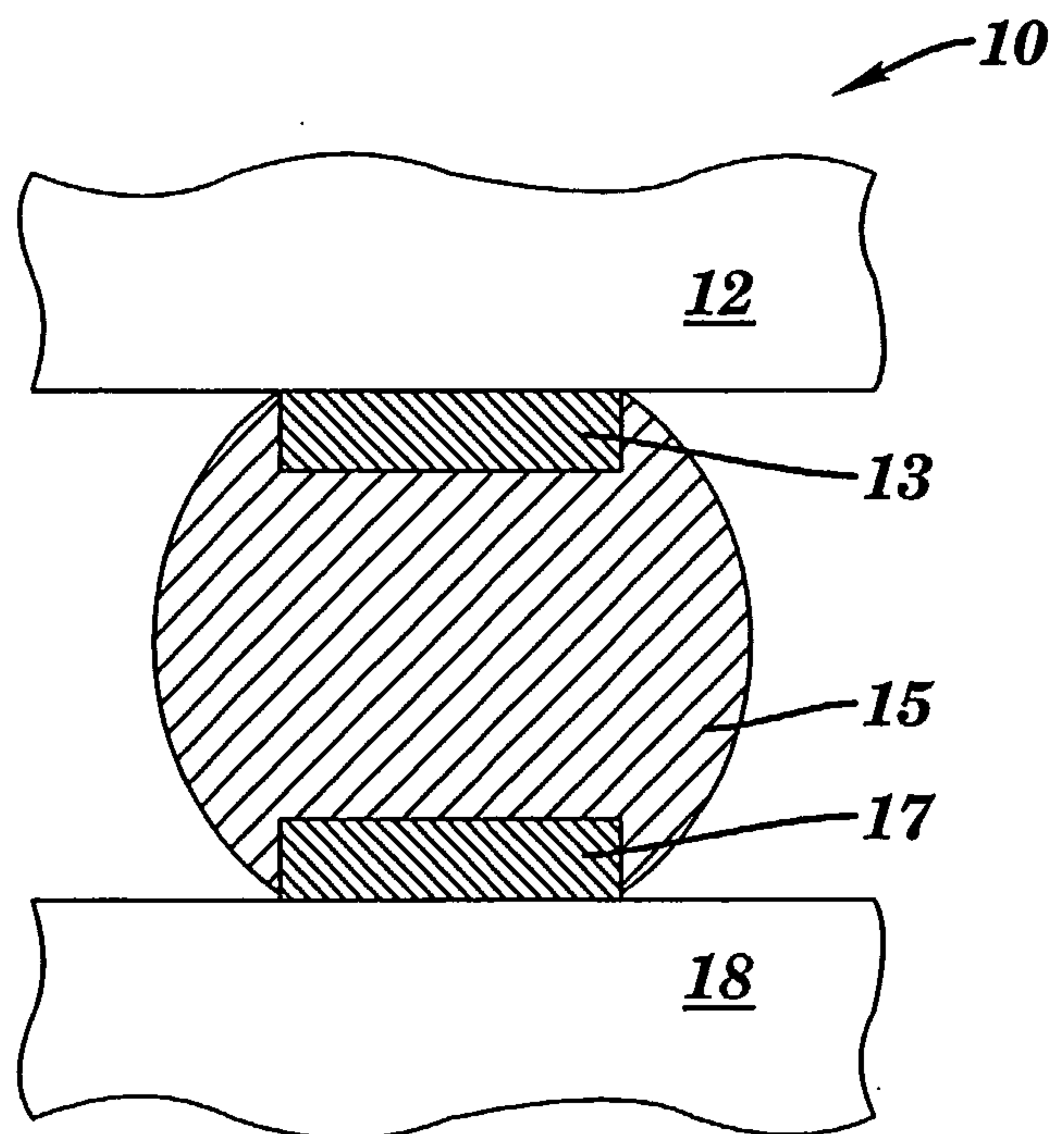

FIG. 1B

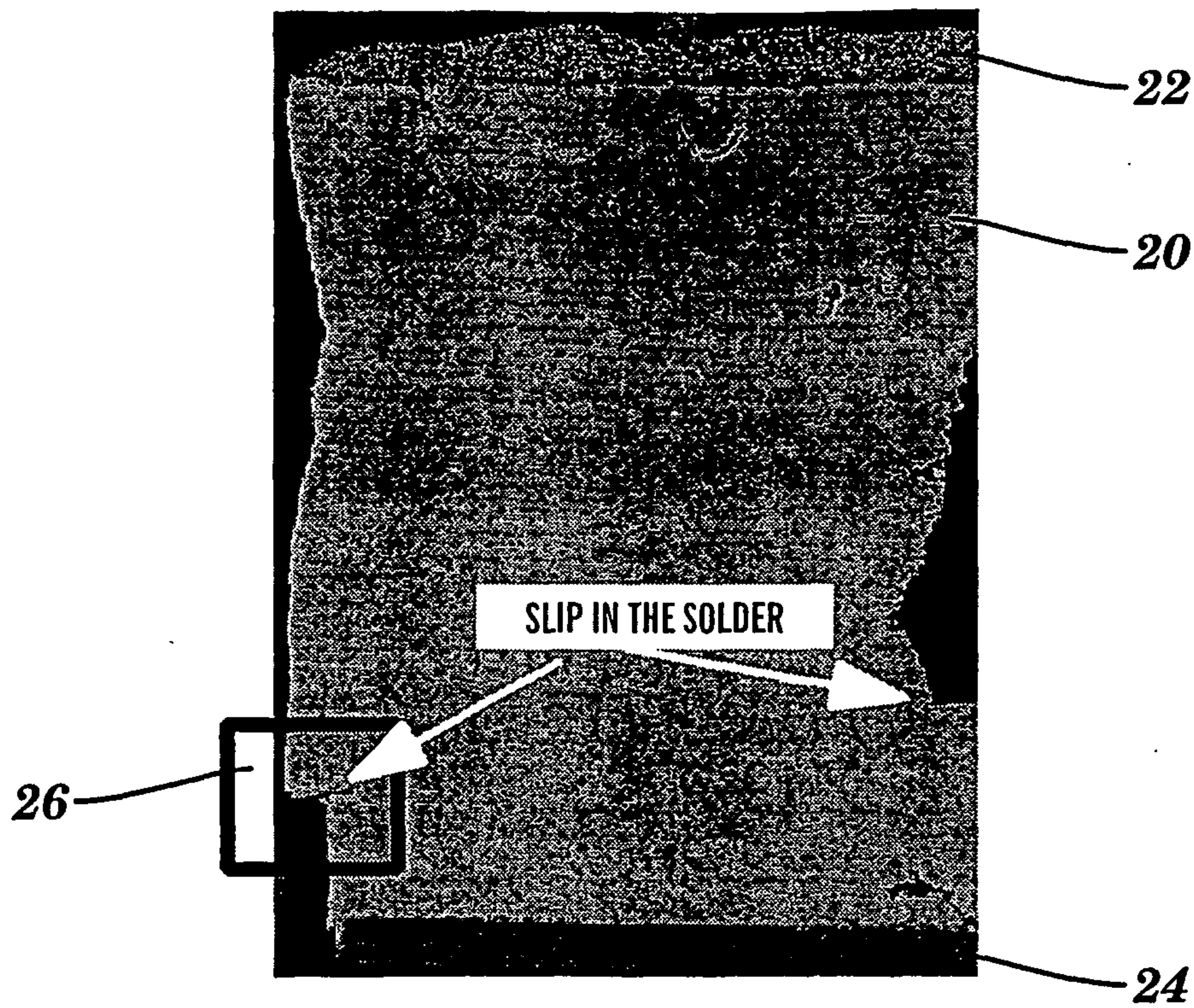

FIG. 2A

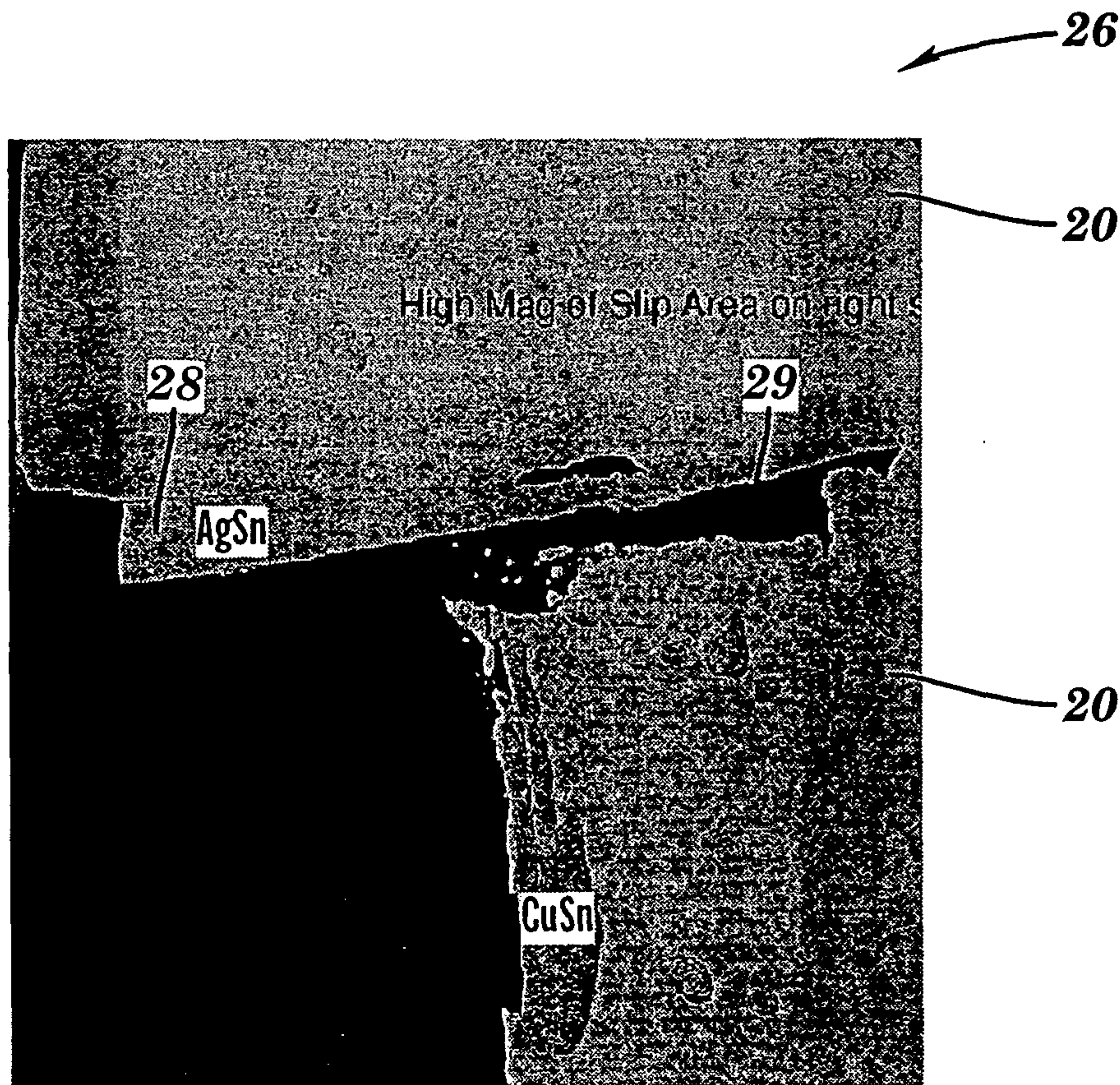

FIG. 2B

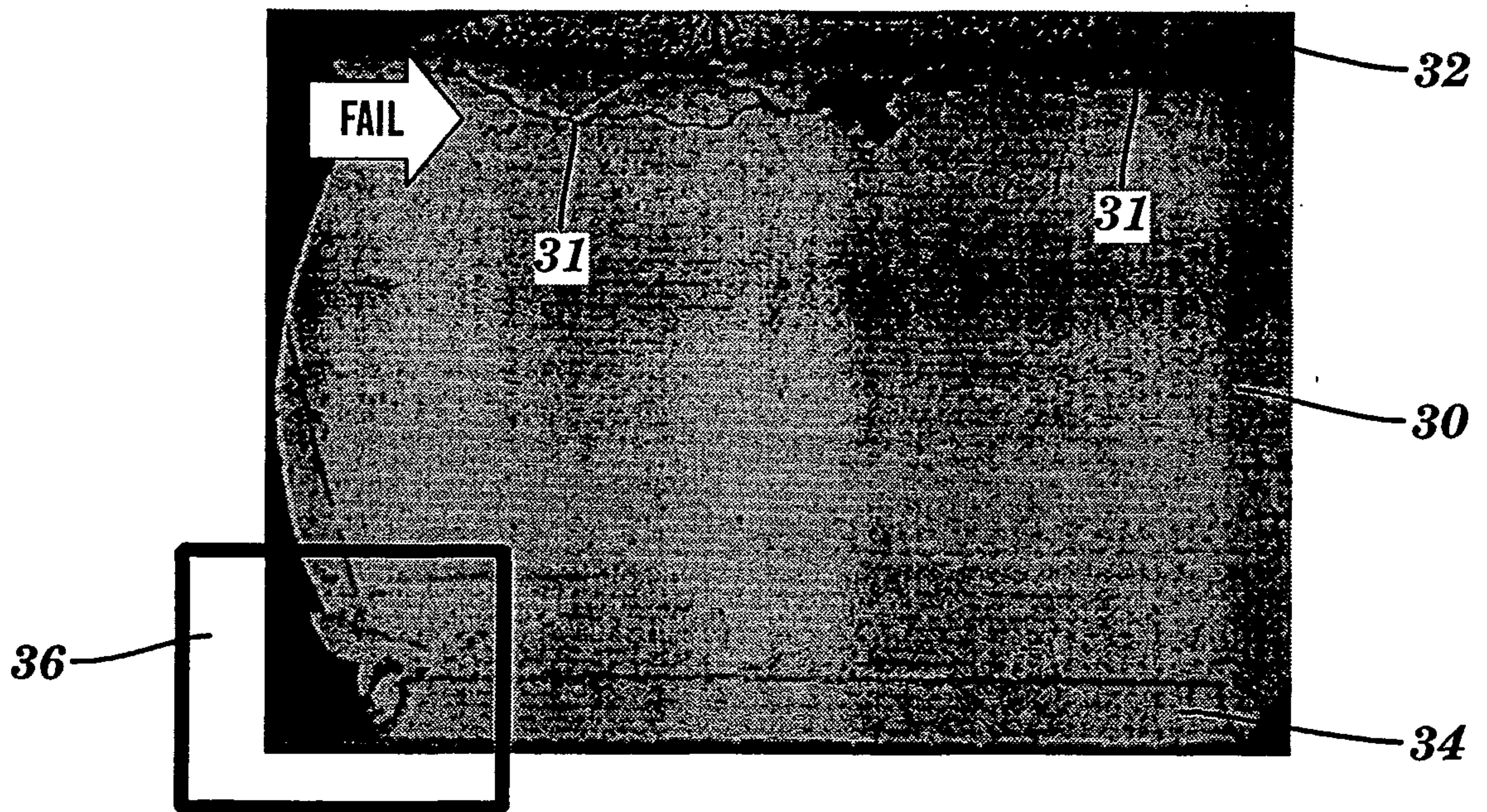

FIG. 3A

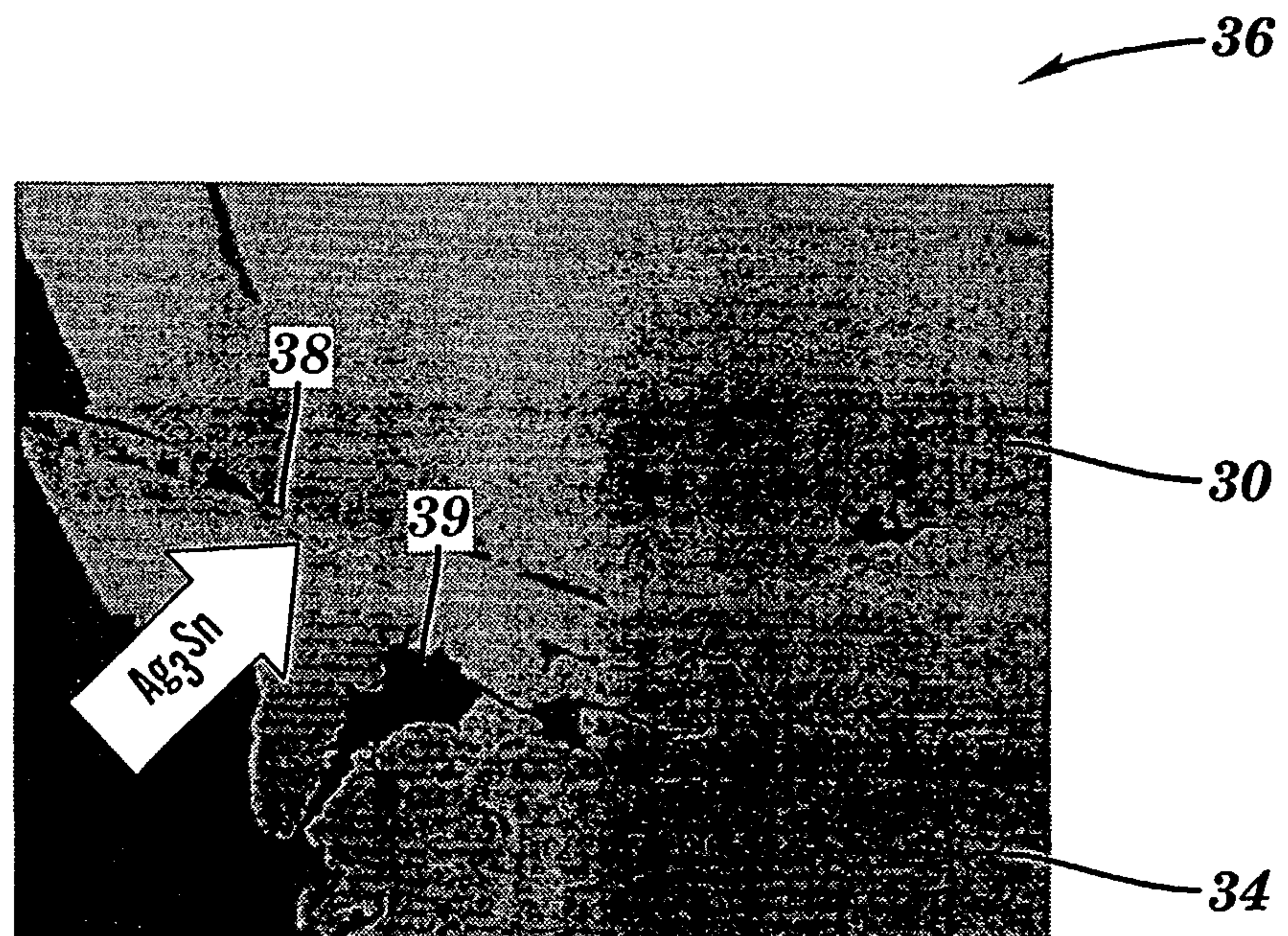

FIG. 3B

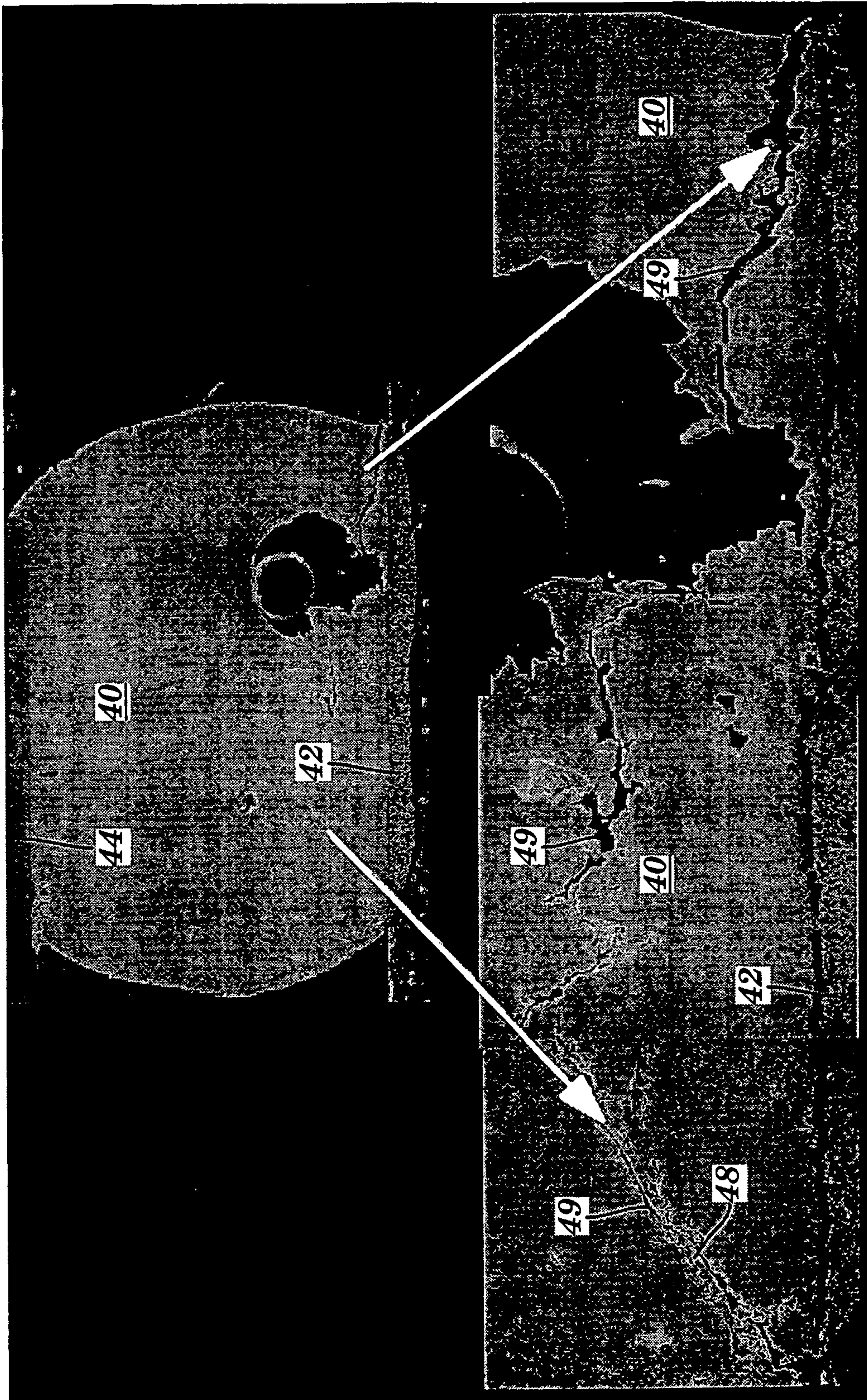

FIG. 3C

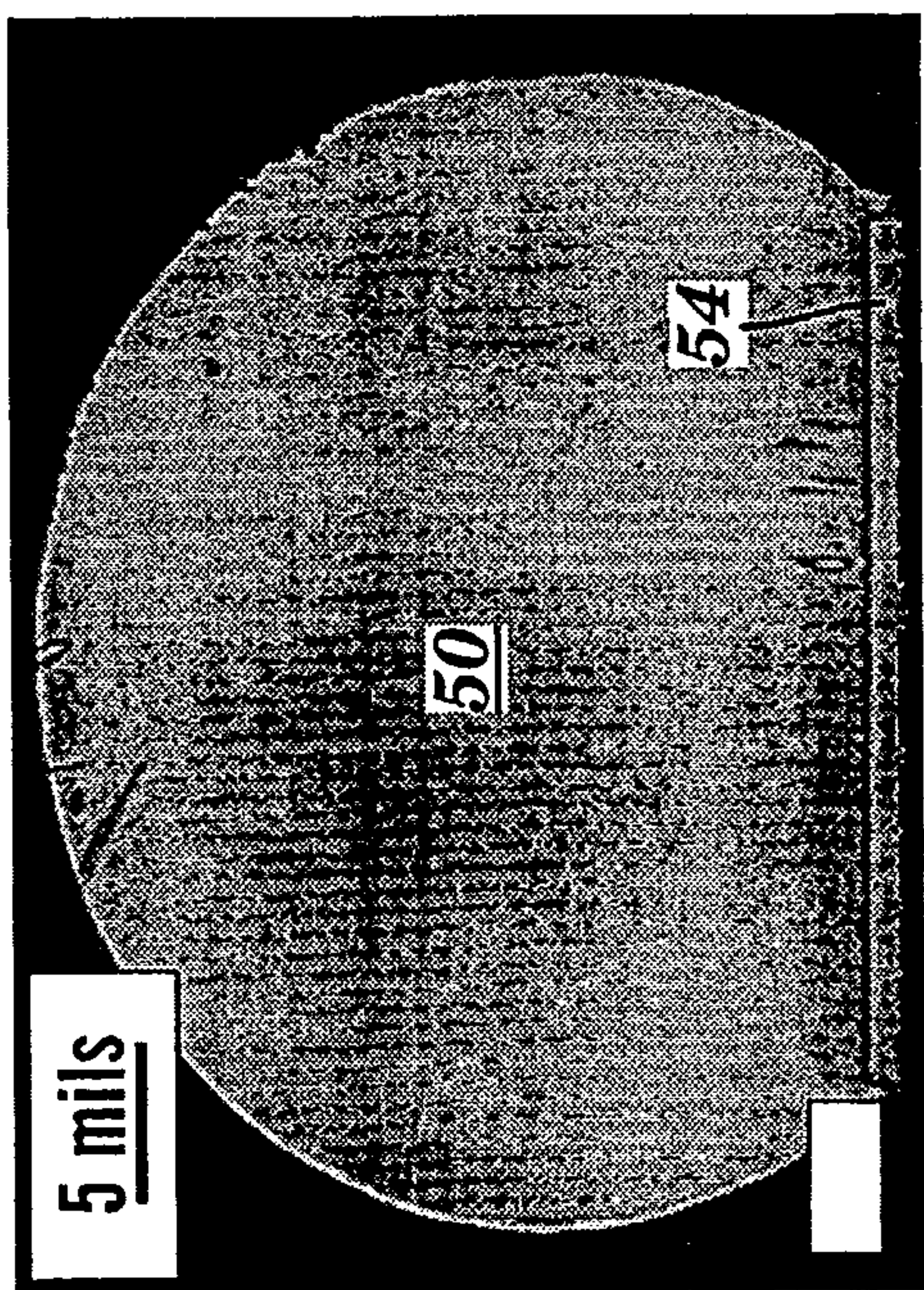

FIG. 4A

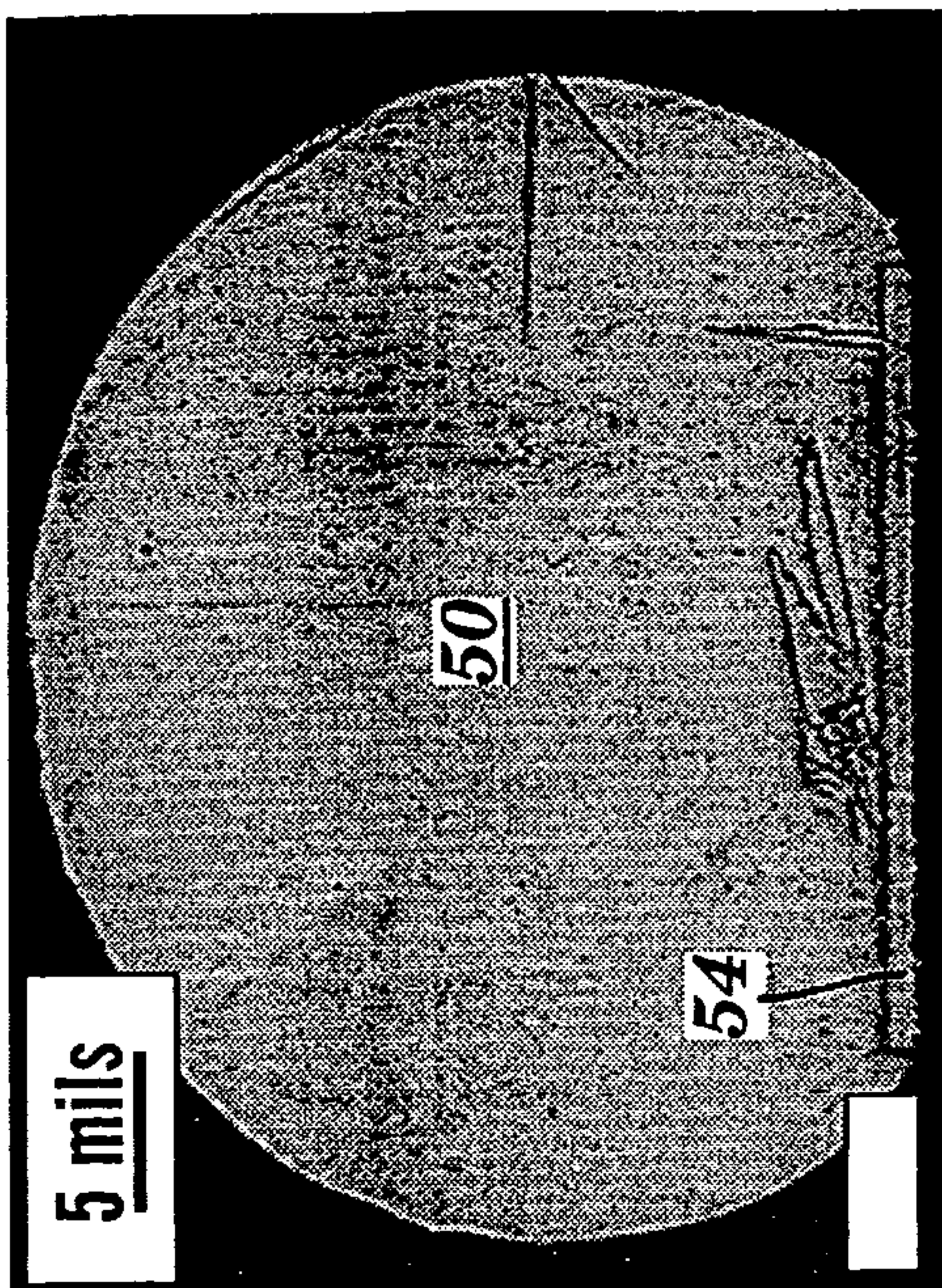

FIG. 4B

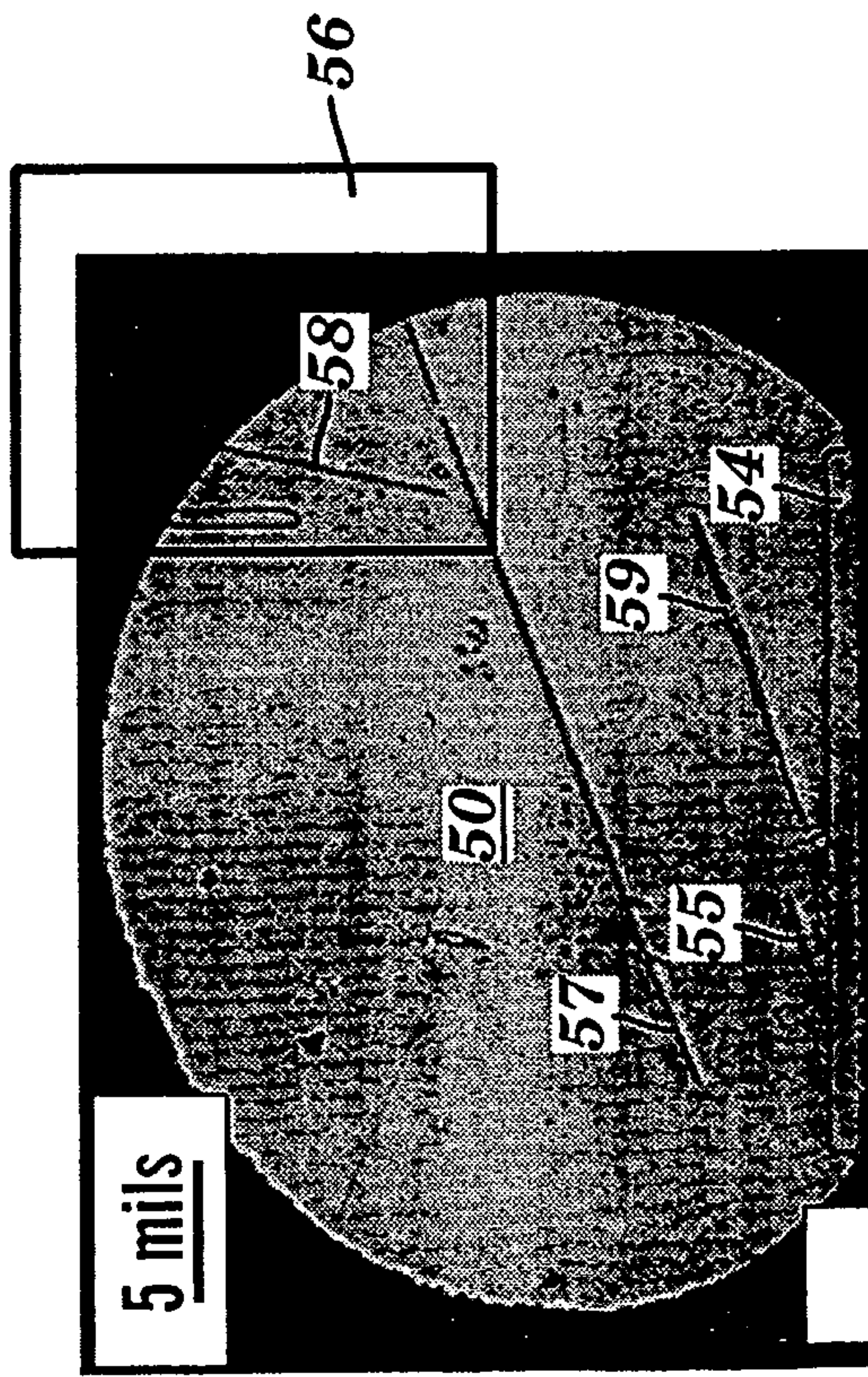

FIG. 4C

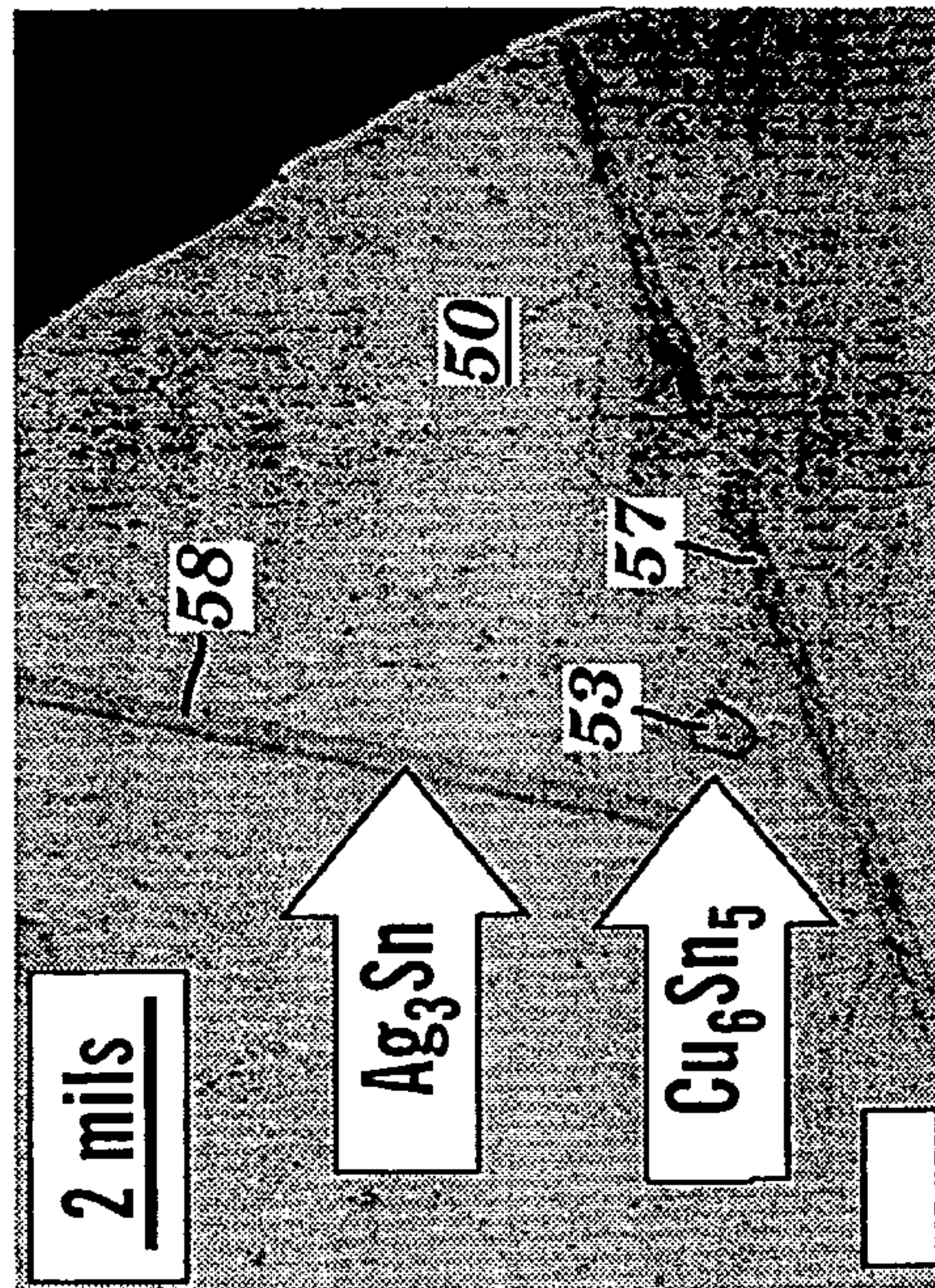

FIG. 4D

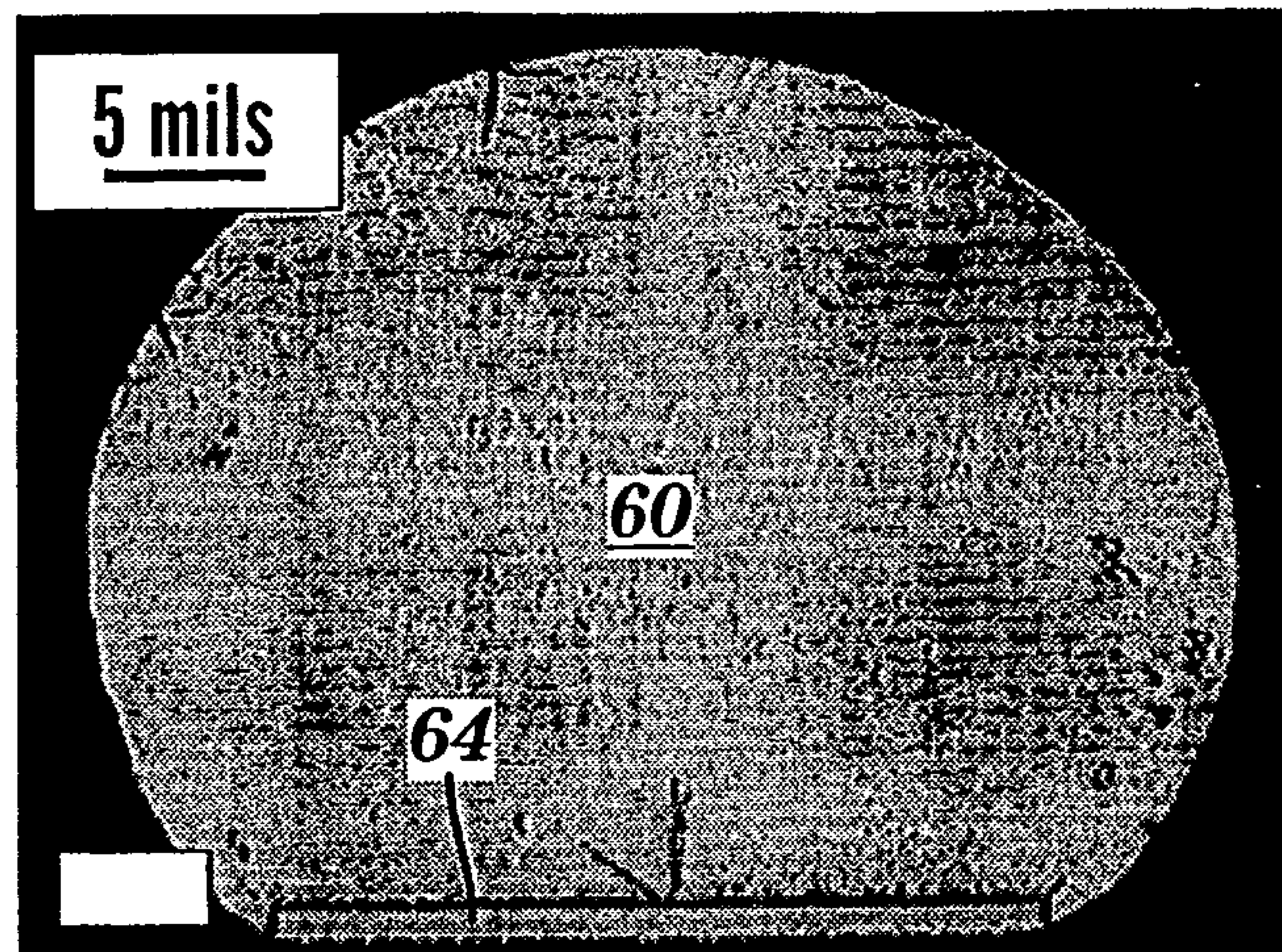

FIG. 5A

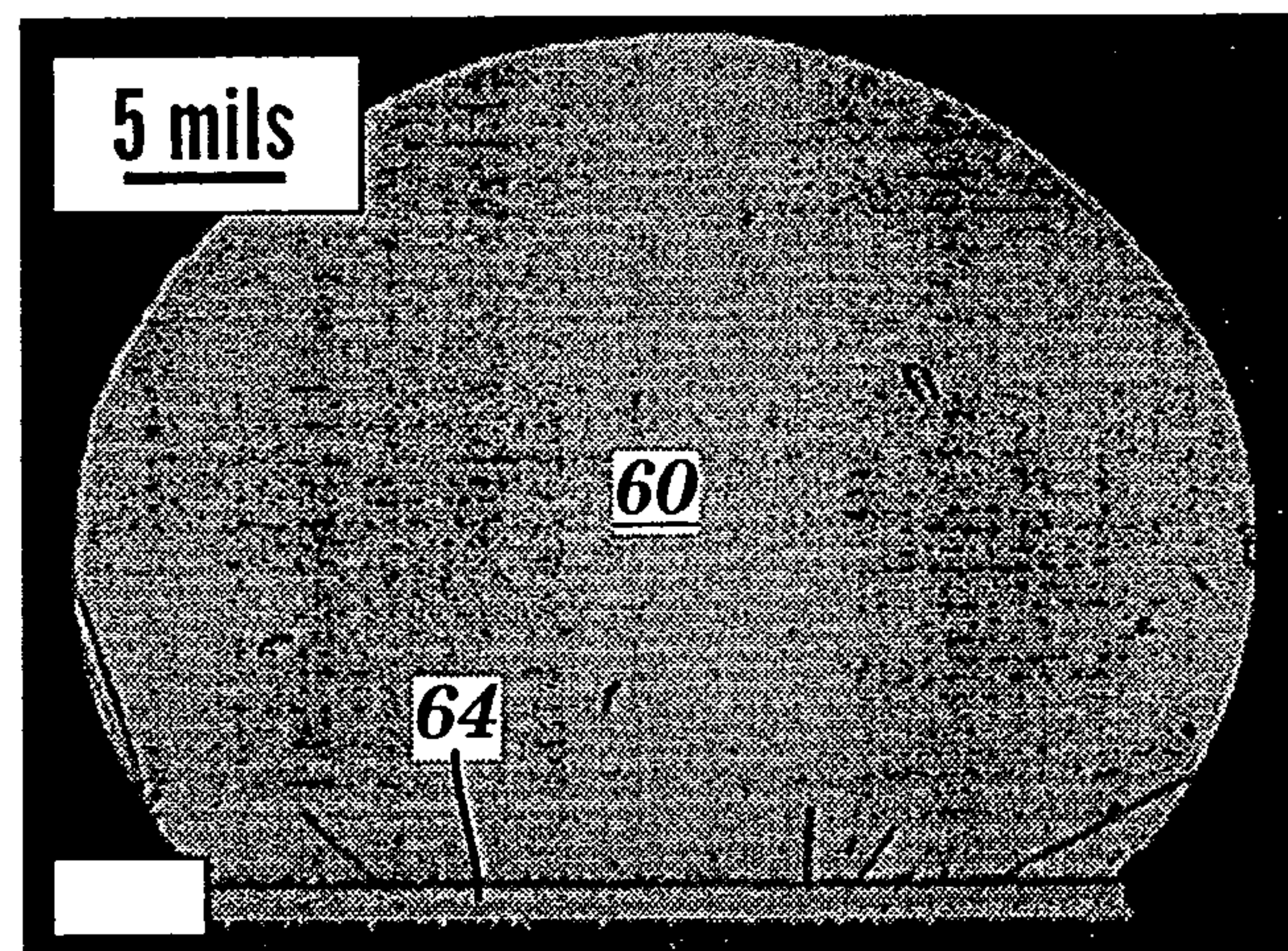

FIG. 5B

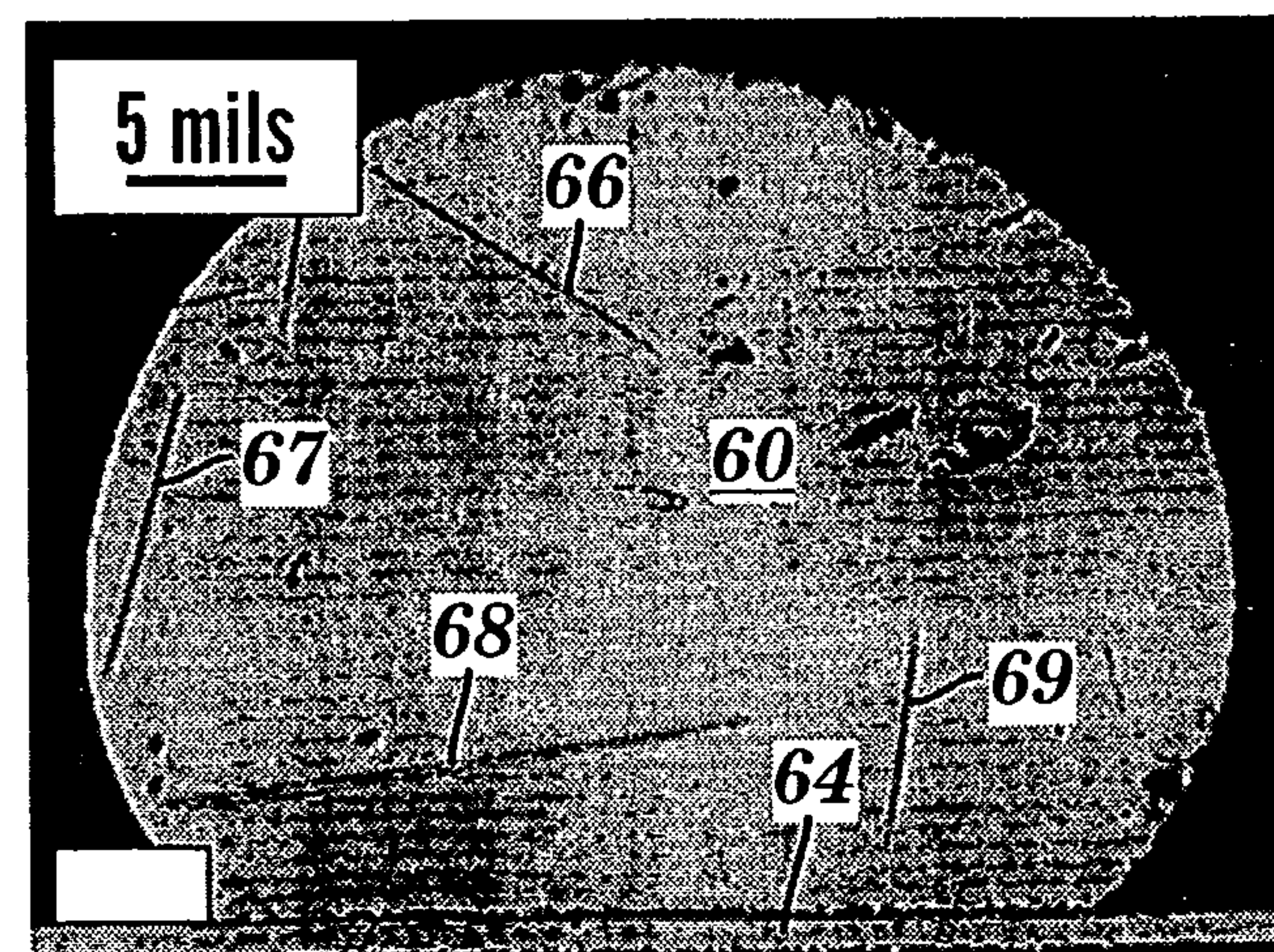

FIG. 5C

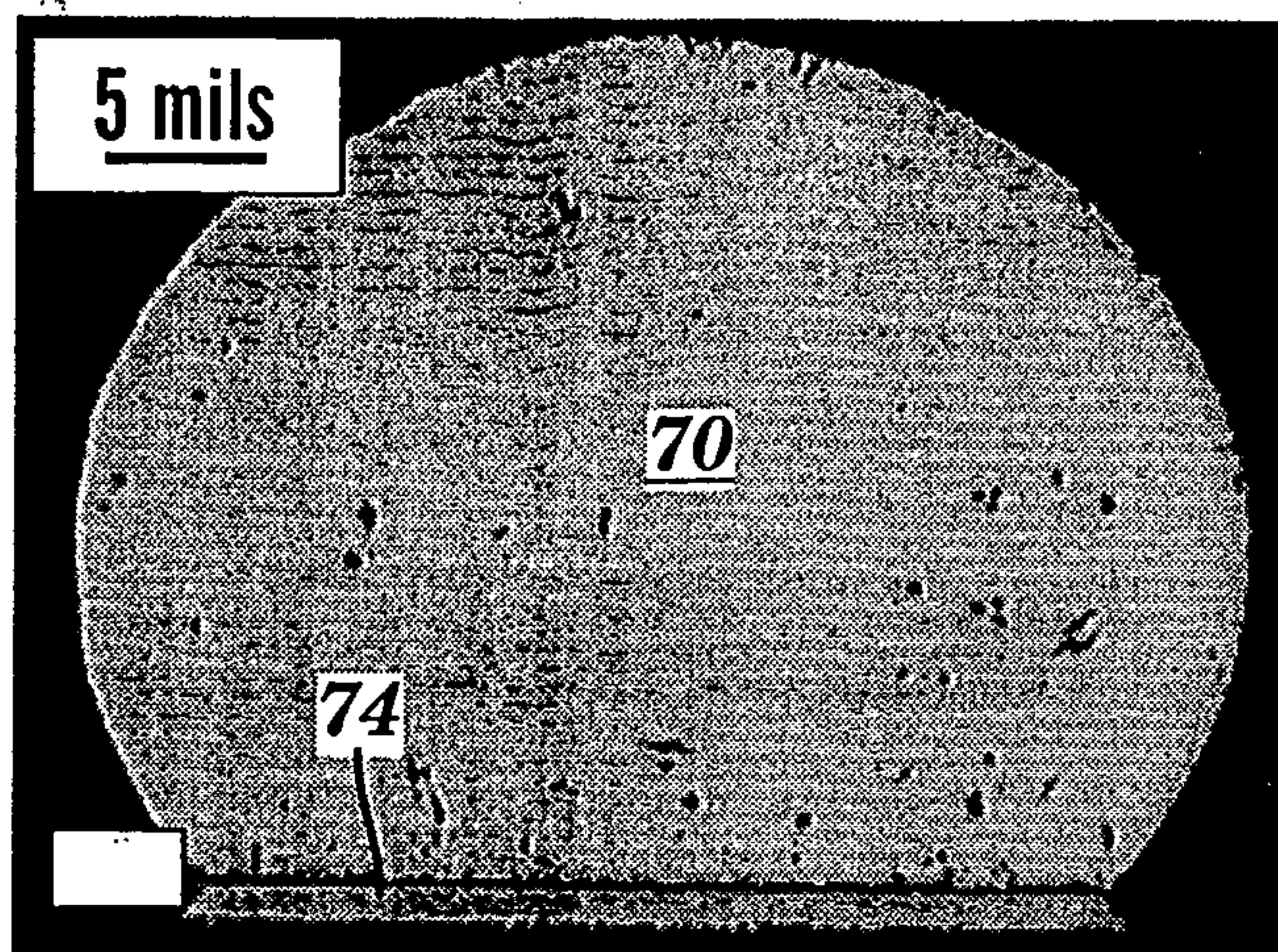

FIG. 6A

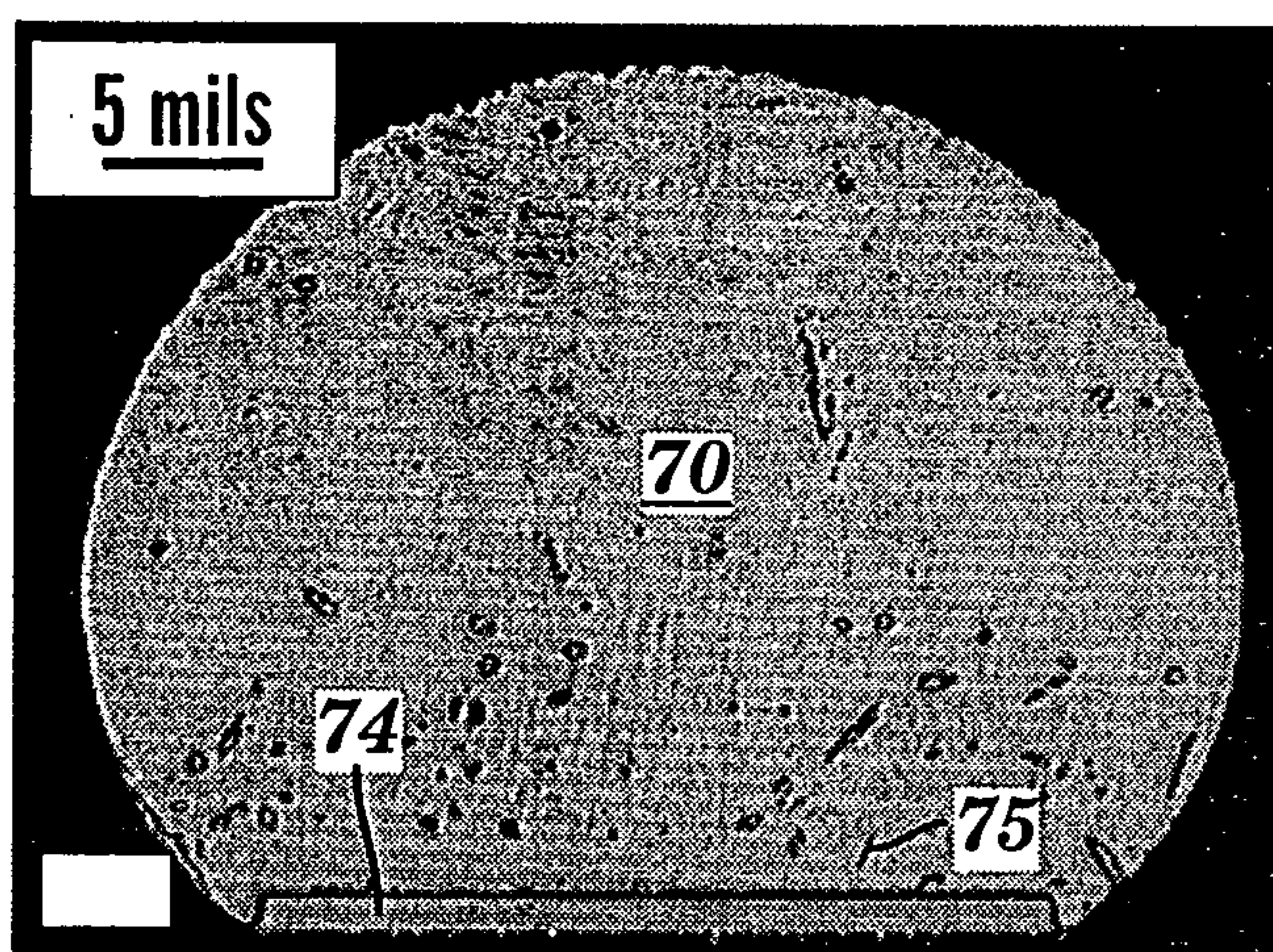

FIG. 6B

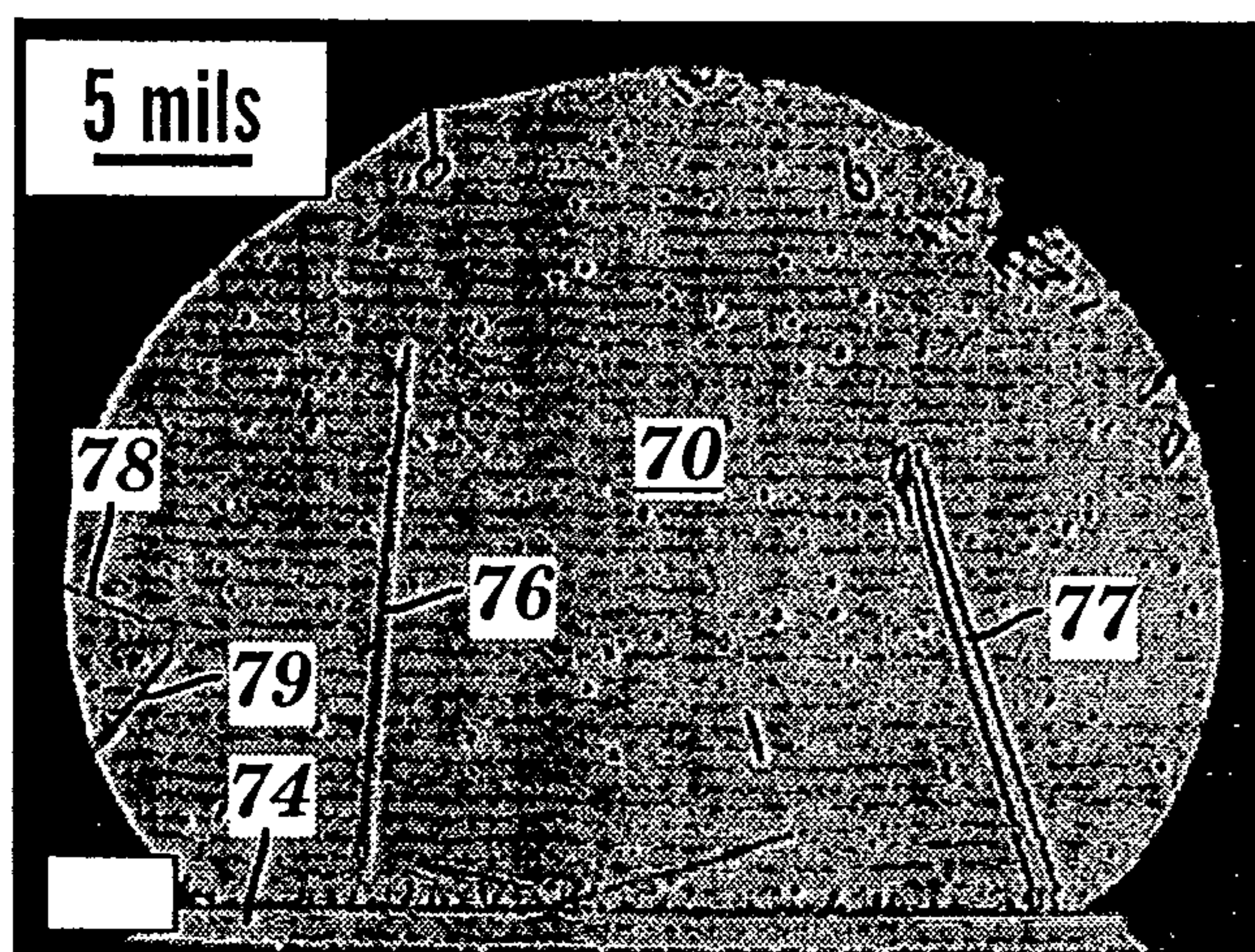

FIG. 6C

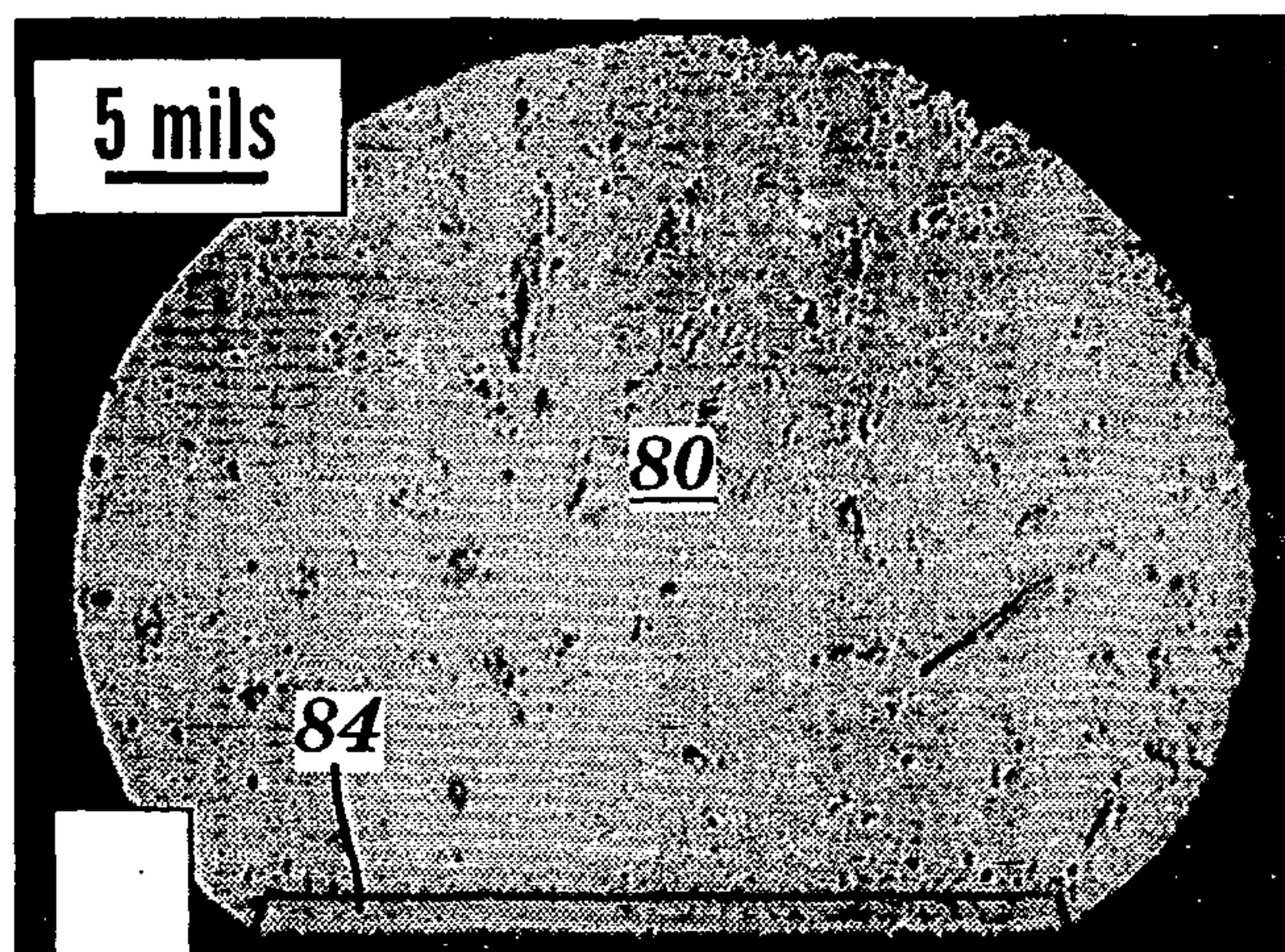

FIG. 7A

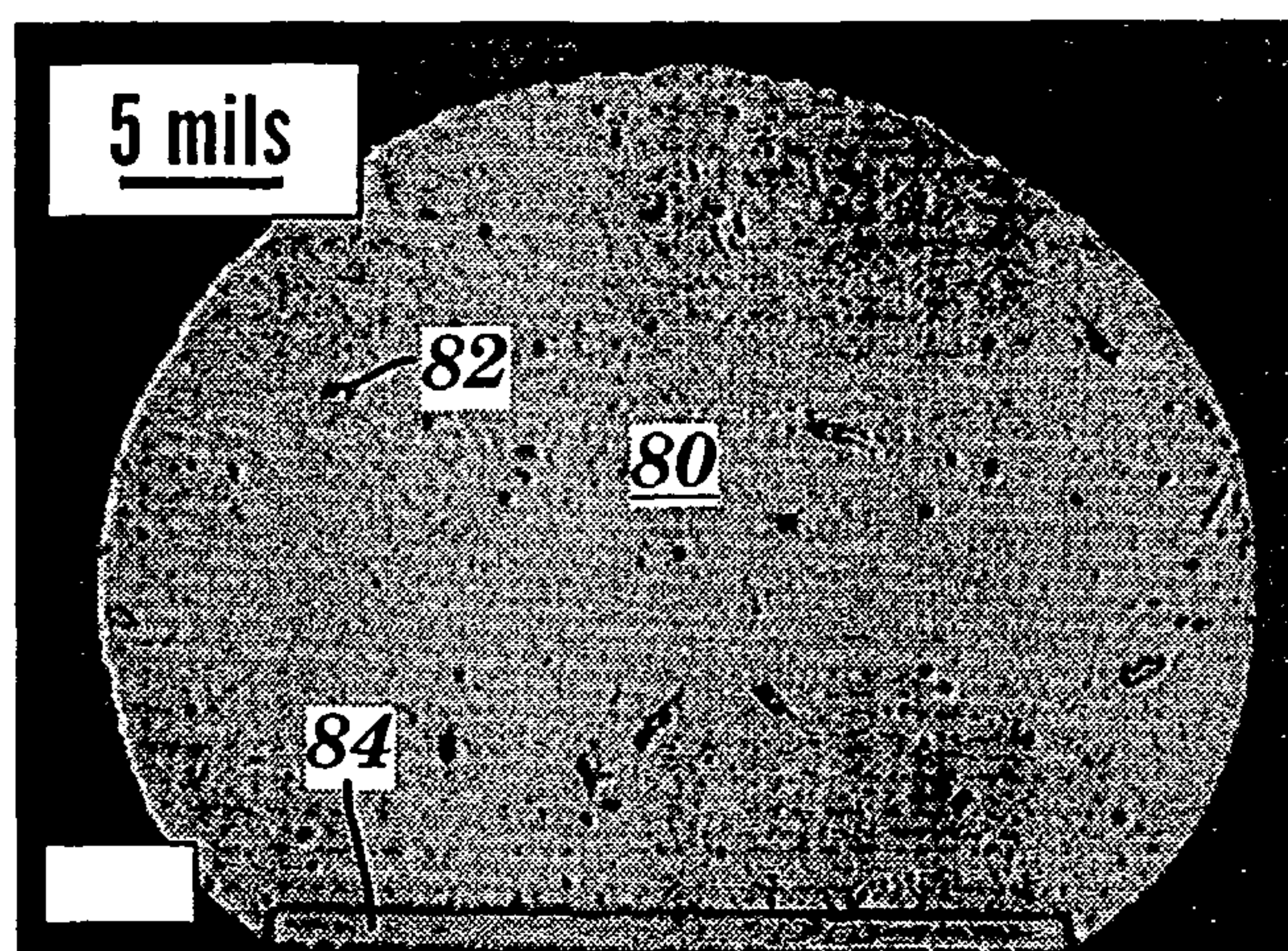

FIG. 7B

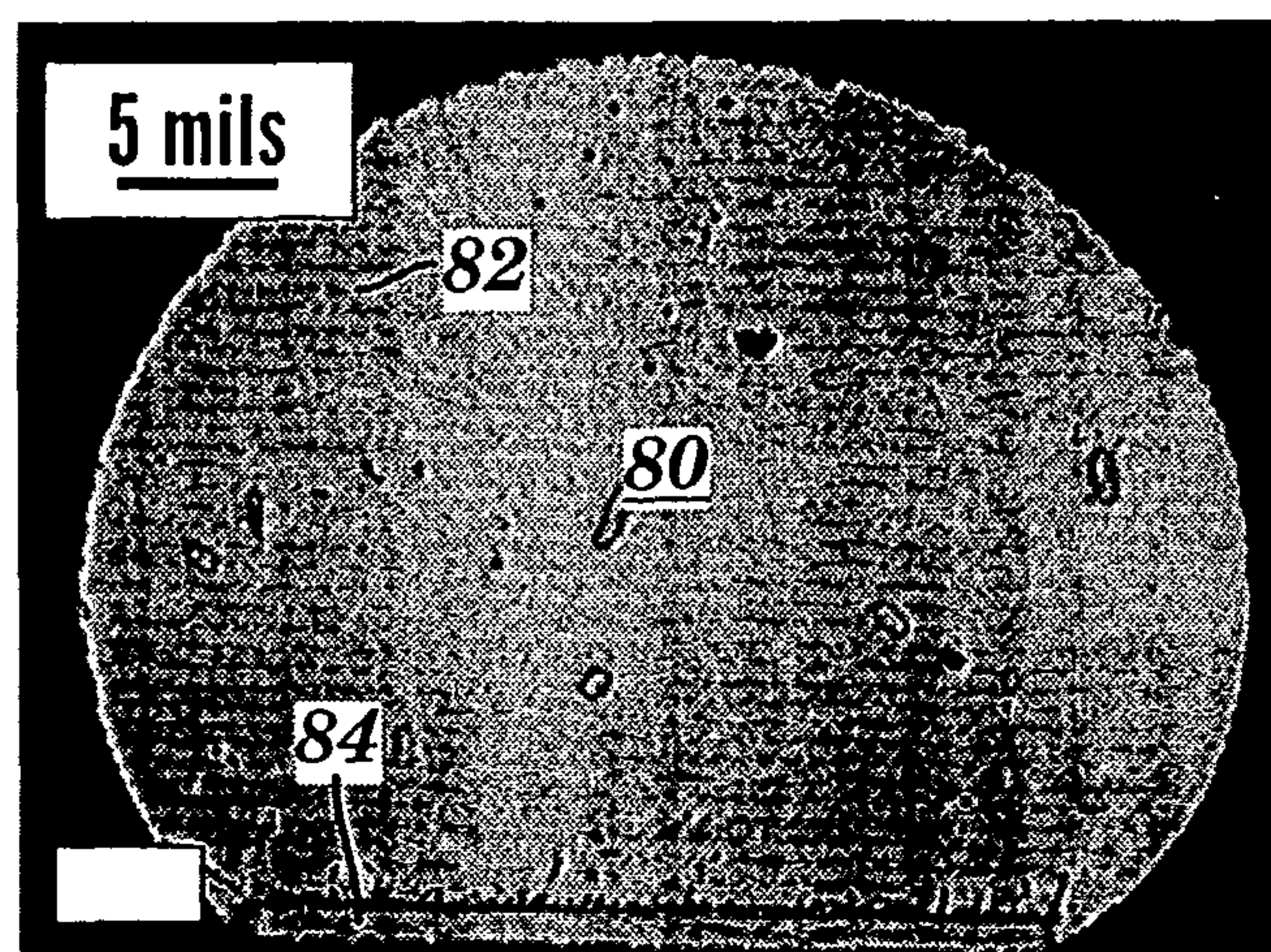

FIG. 7C

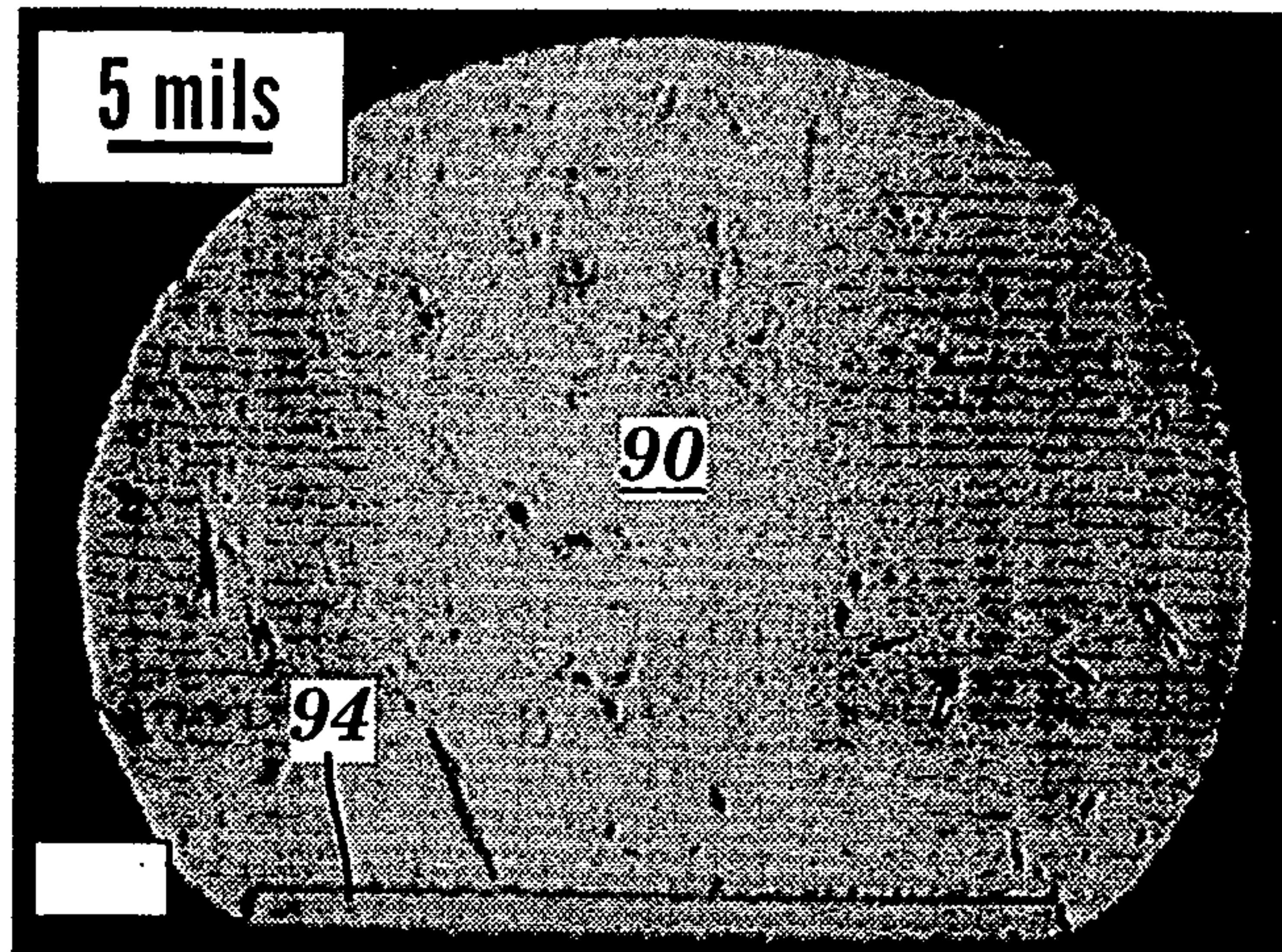

FIG. 8A

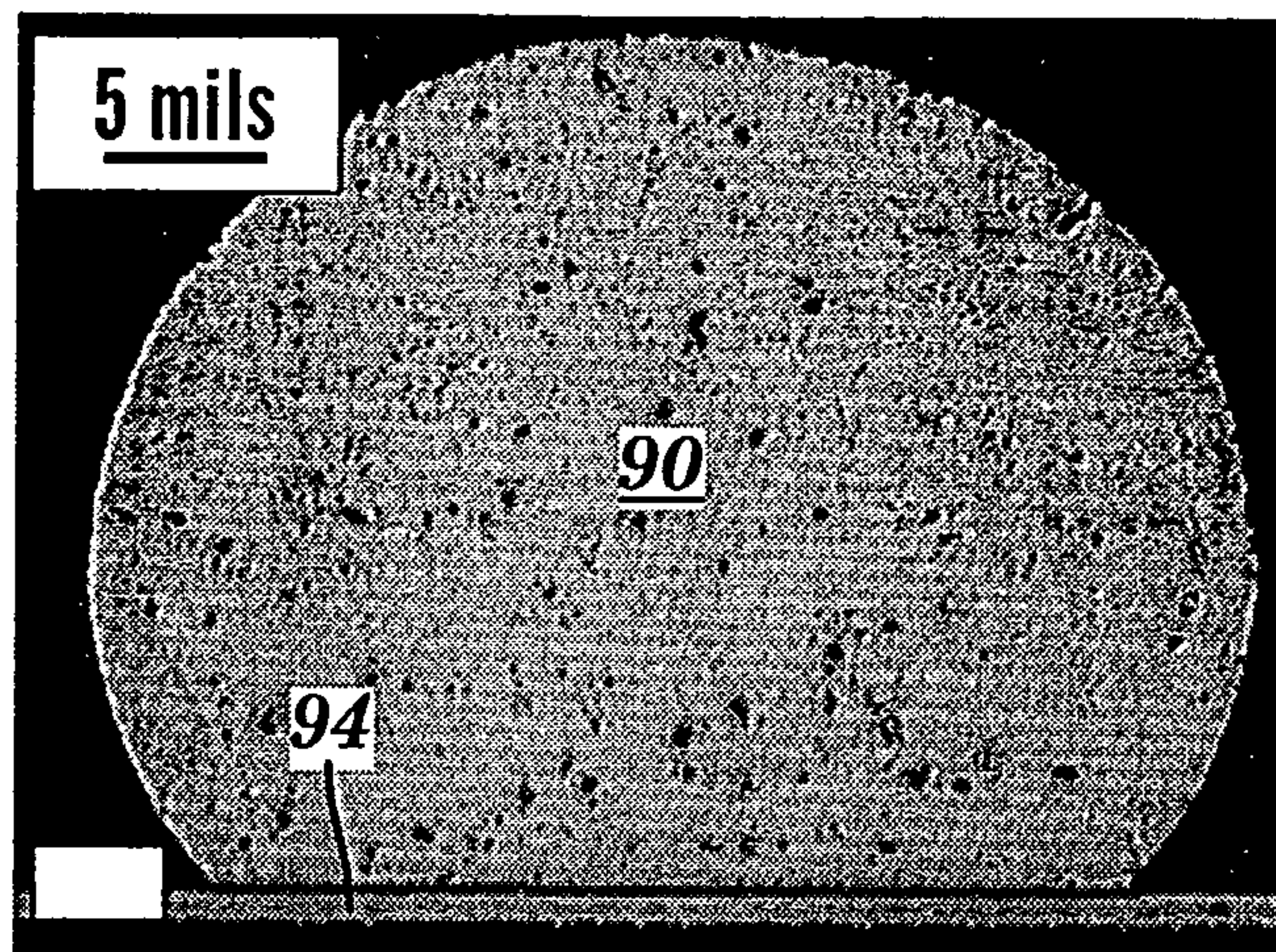

FIG. 8B

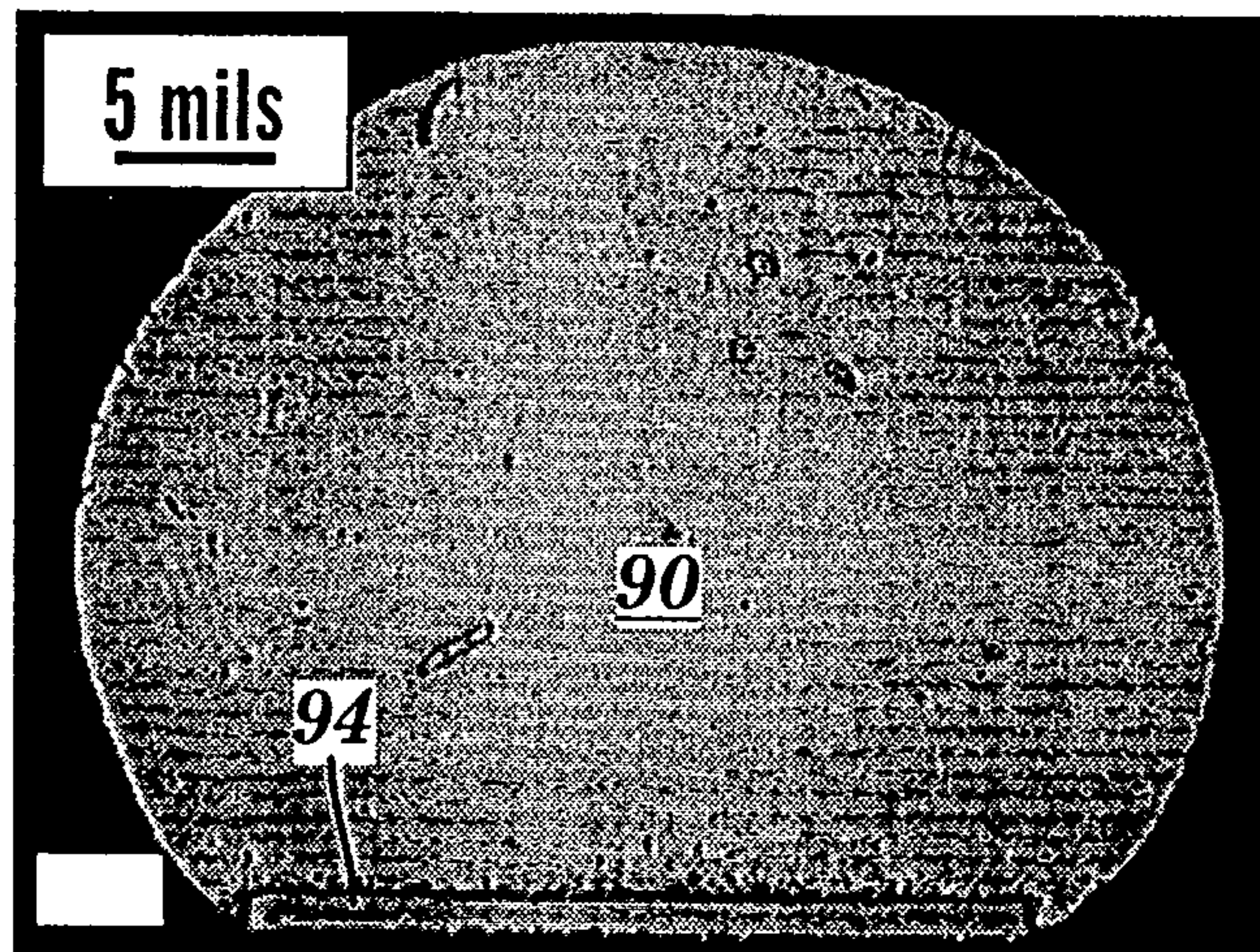

FIG. 8C

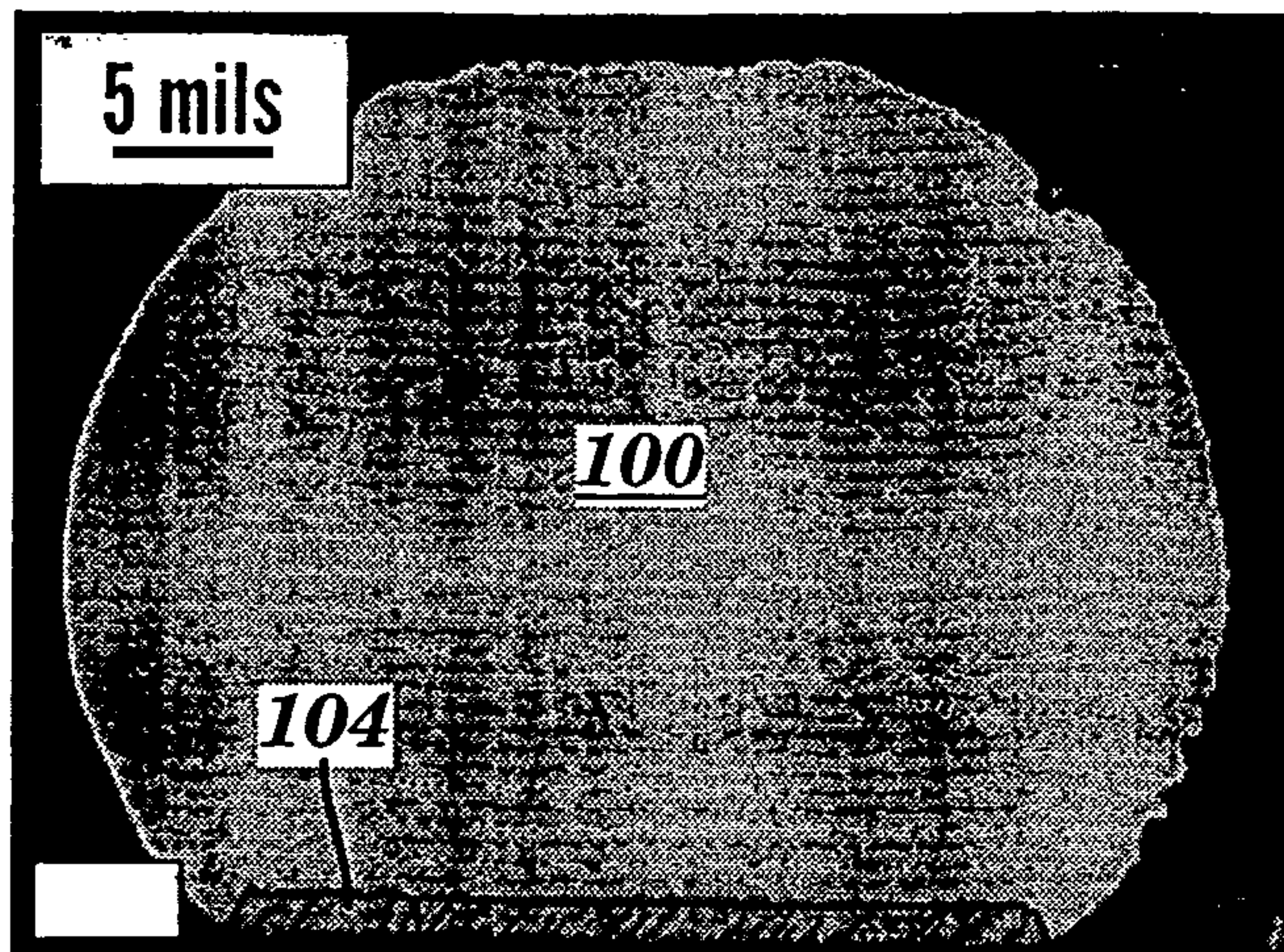

FIG. 9A

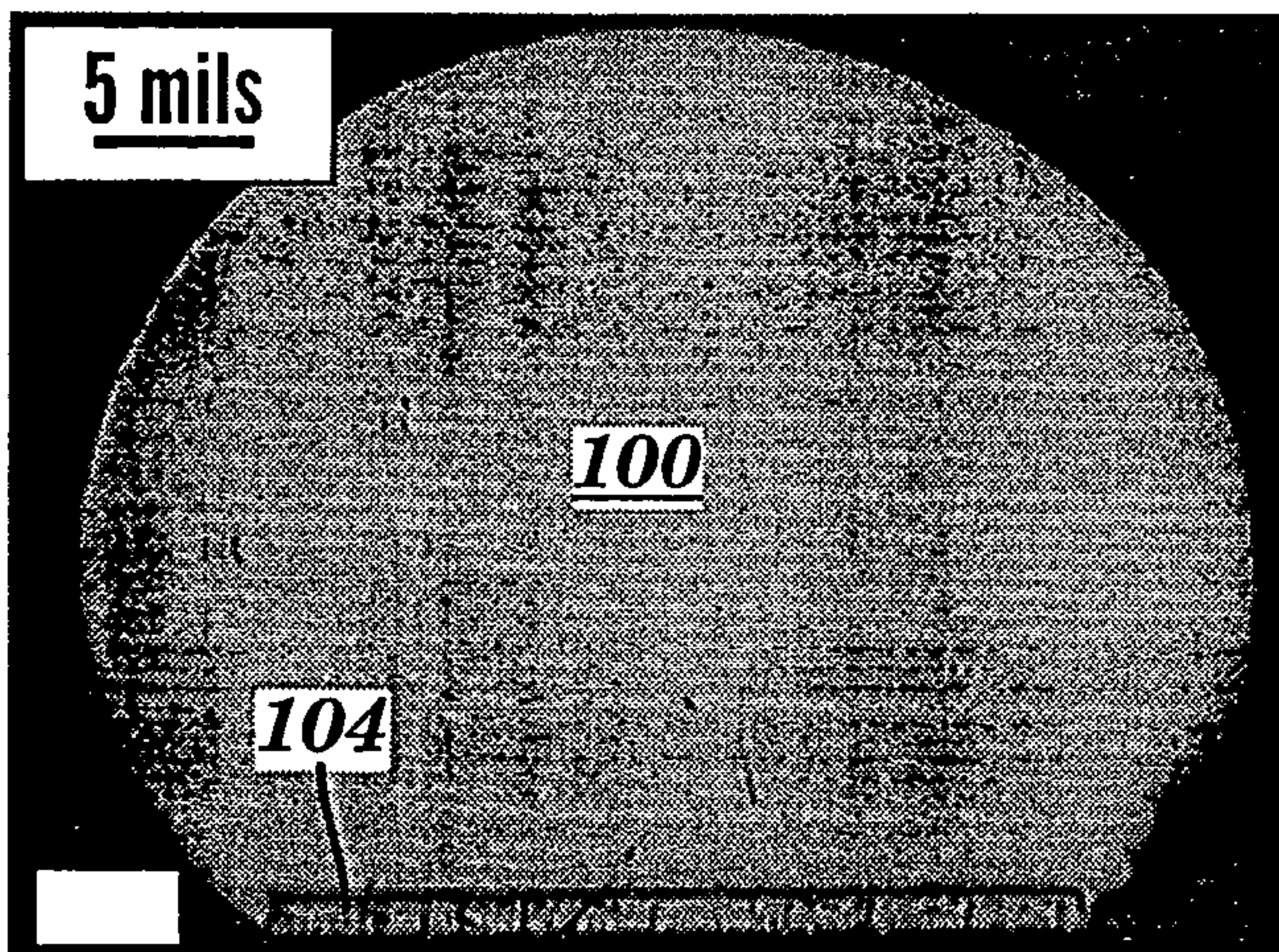

FIG. 9B

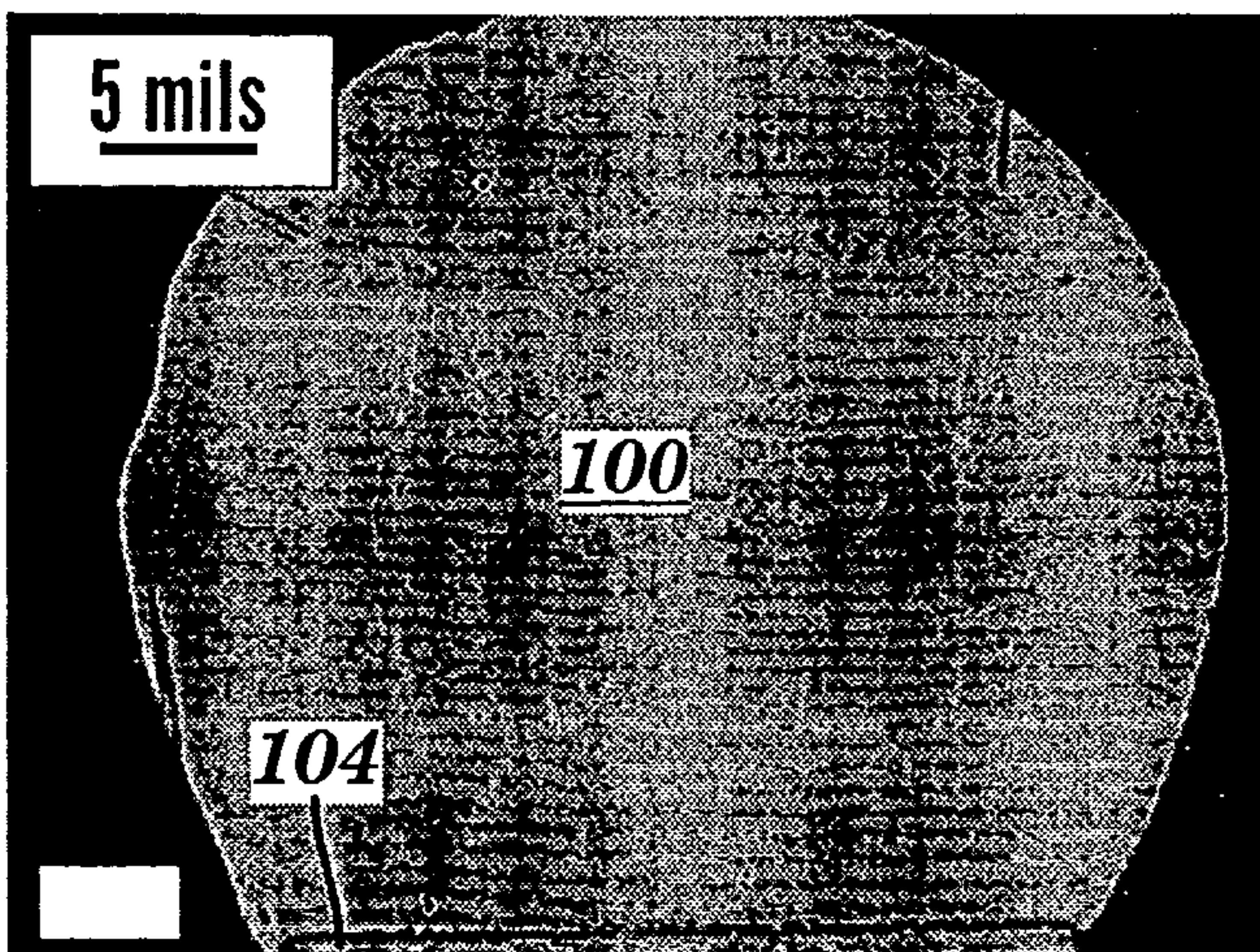

FIG. 9C

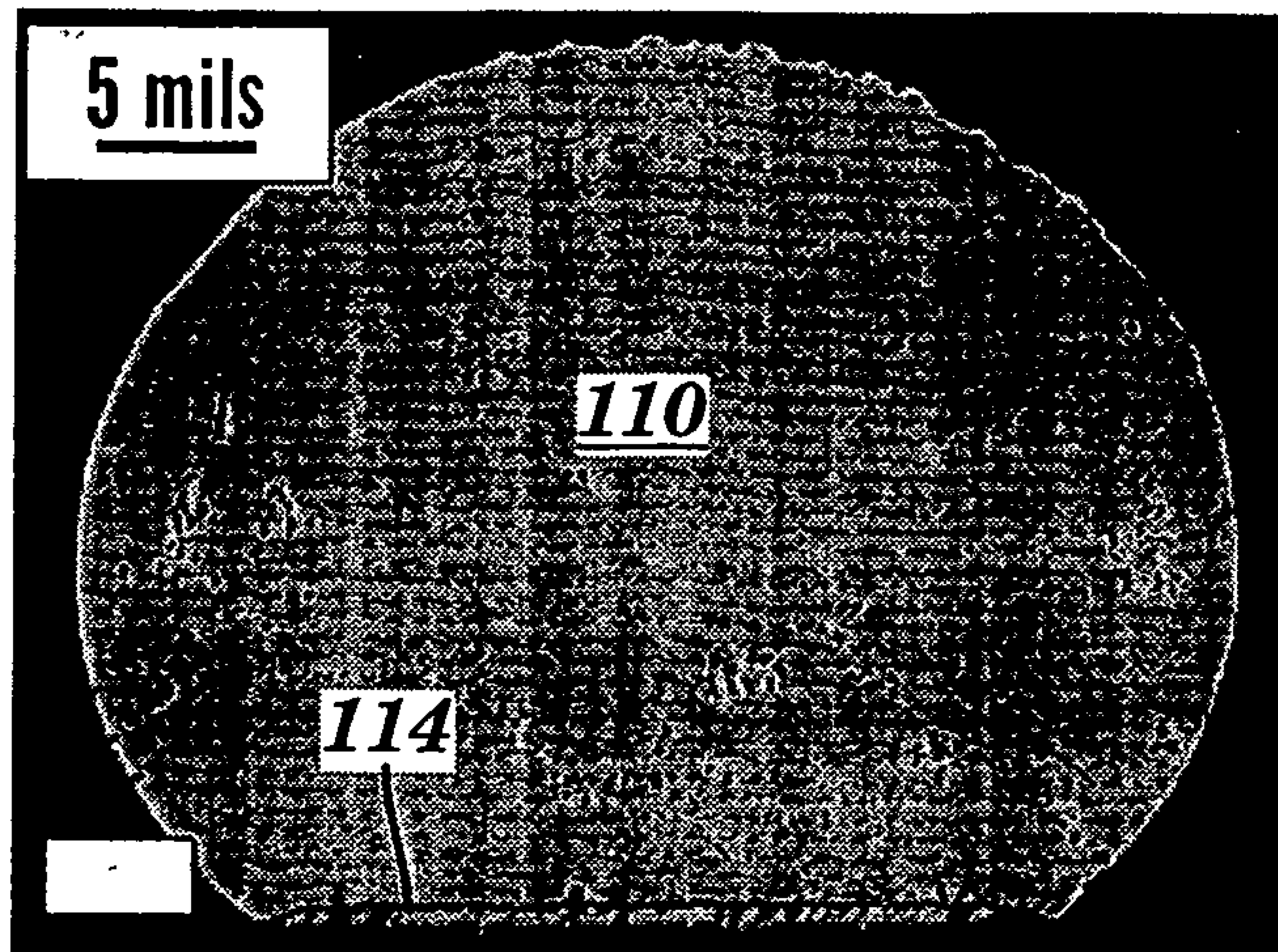

FIG. 10A

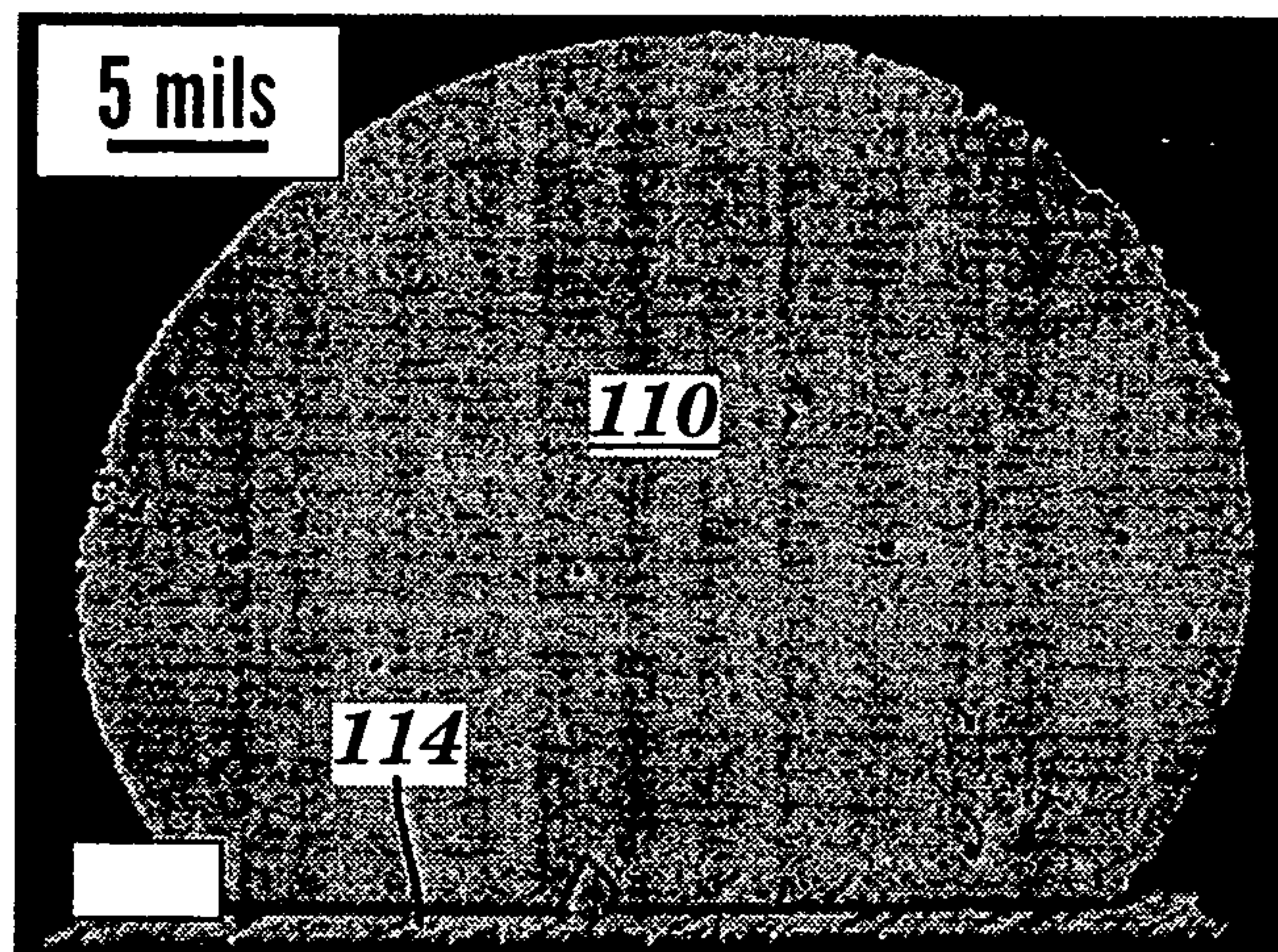

FIG. 10B

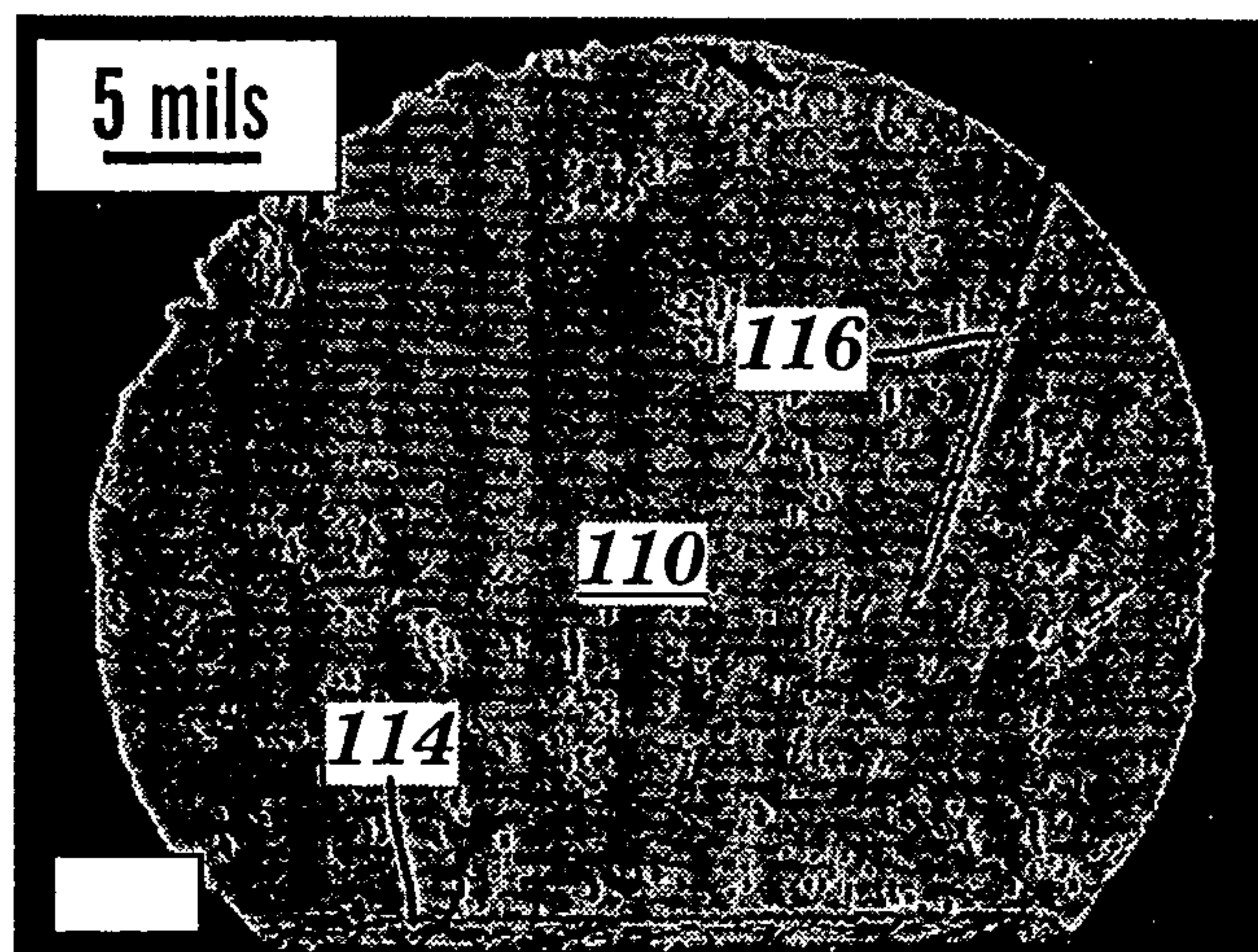

FIG. 10C

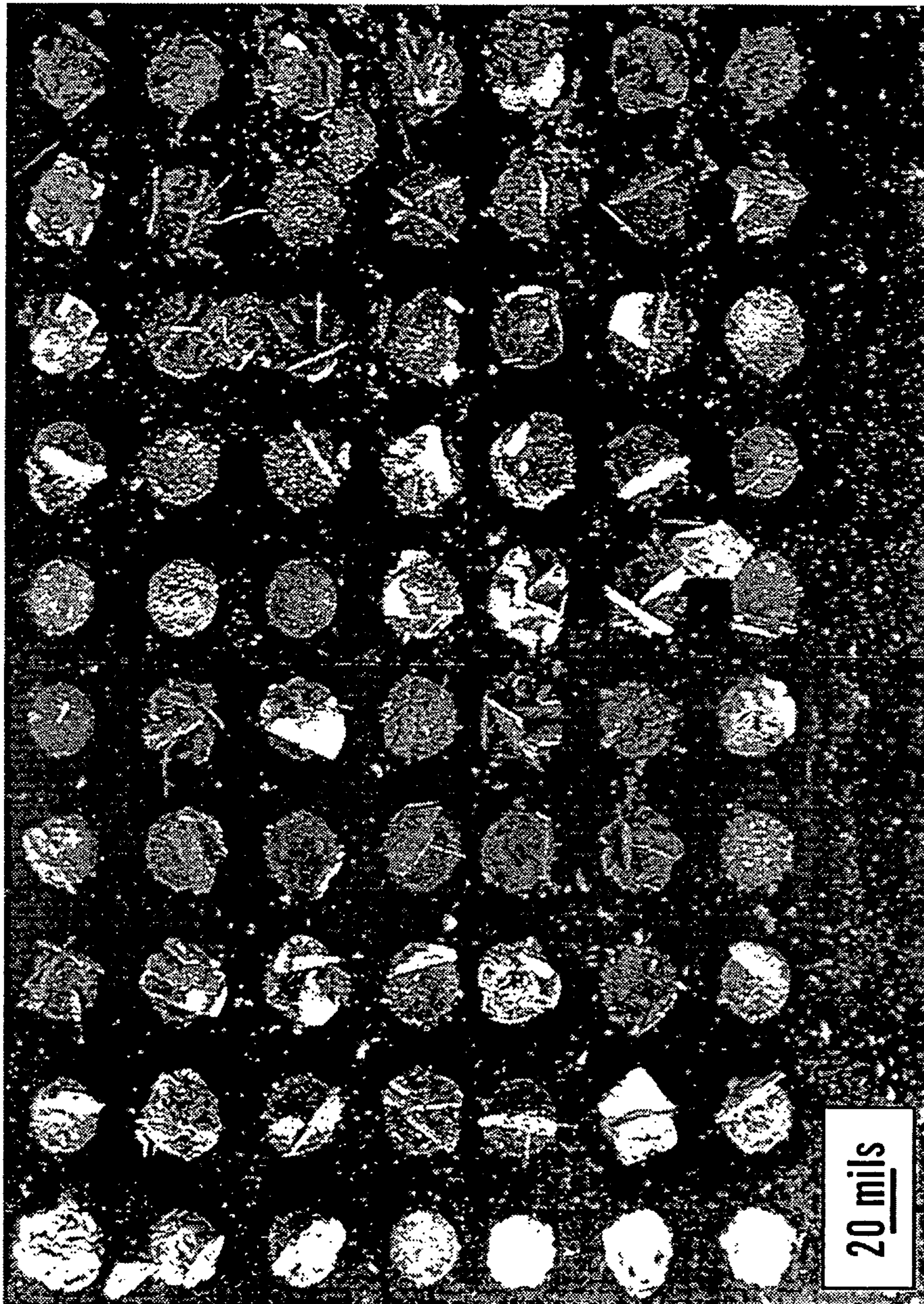

FIG. 11

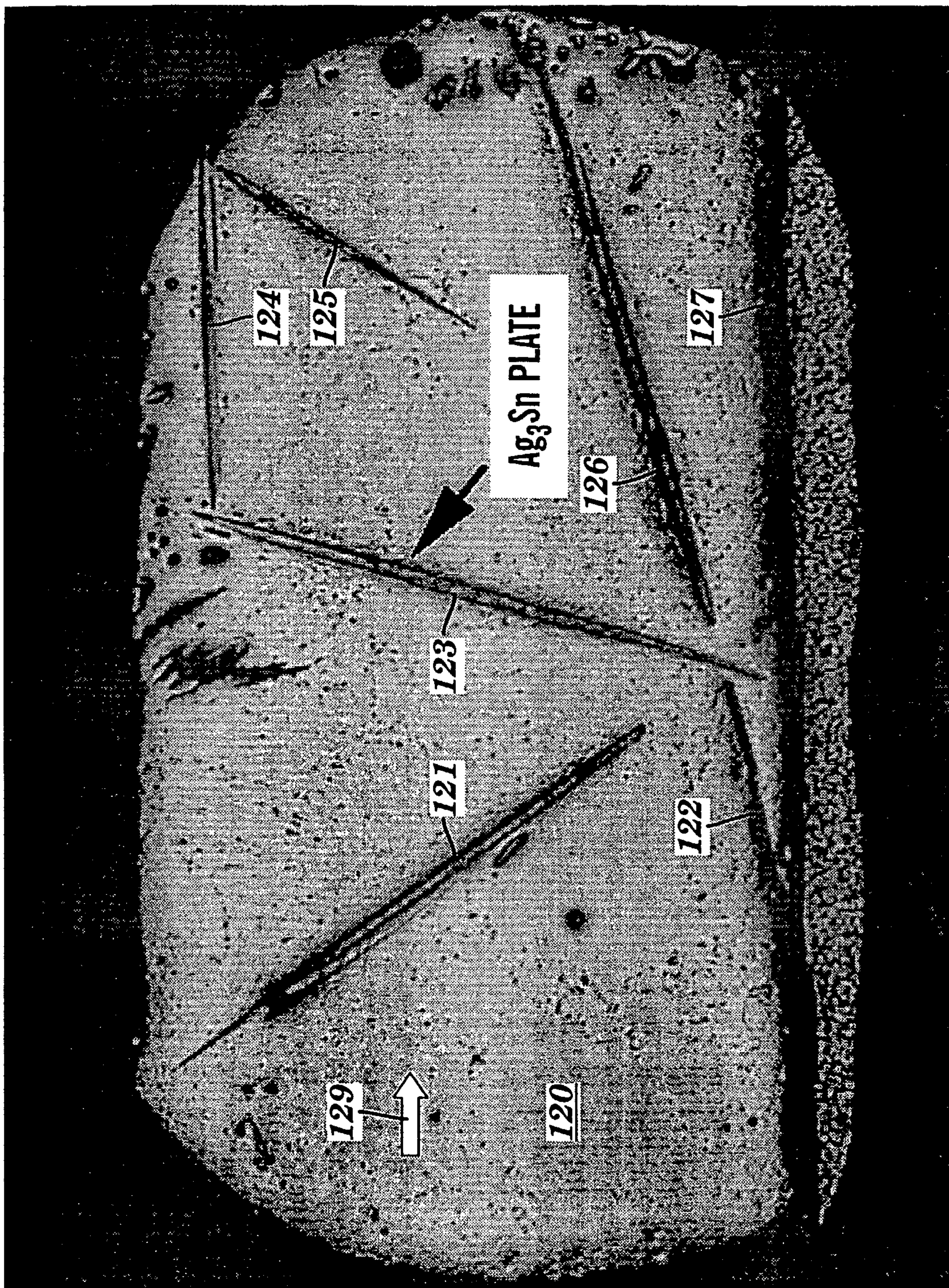

FIG. 12

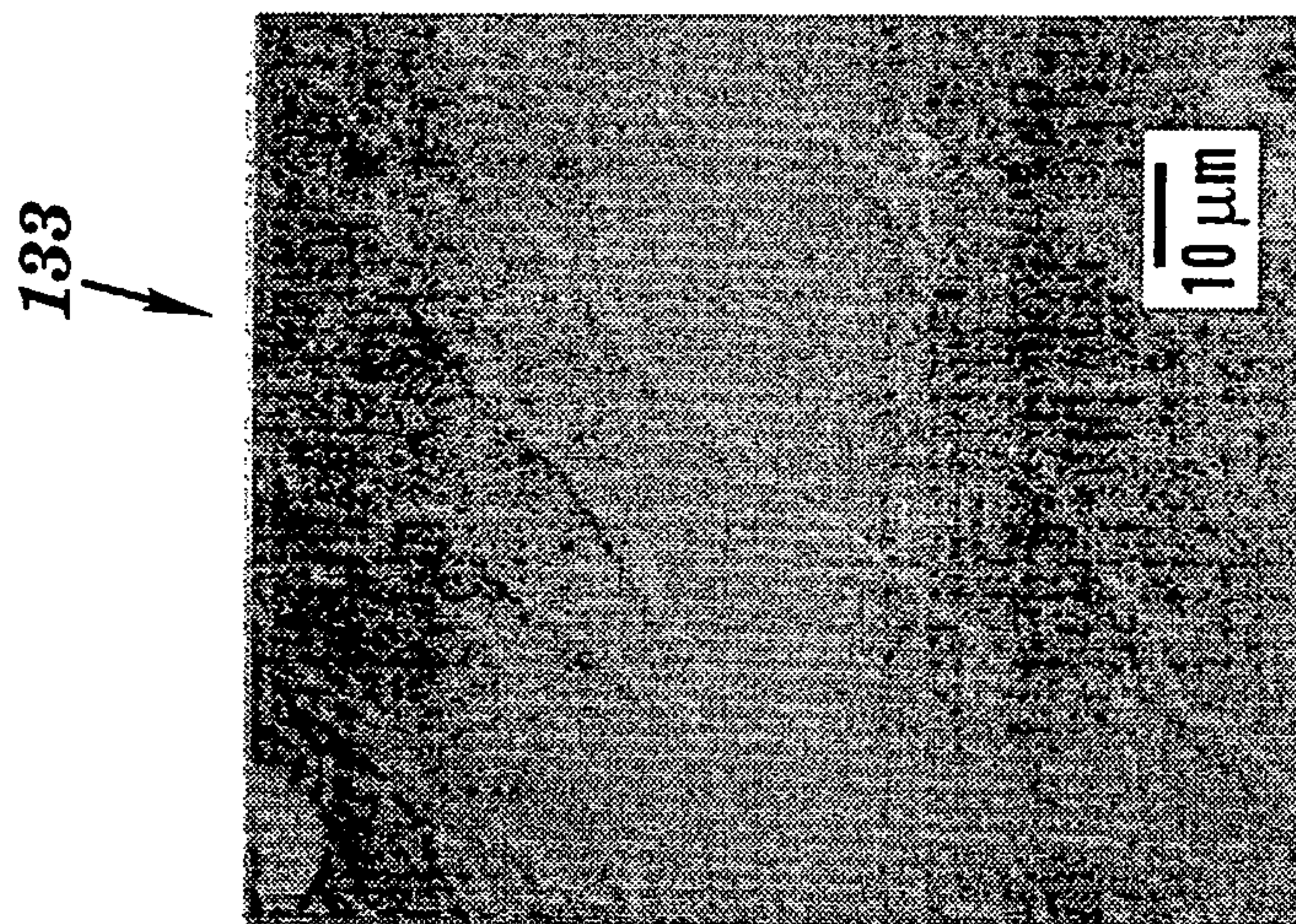

FIG. 13B

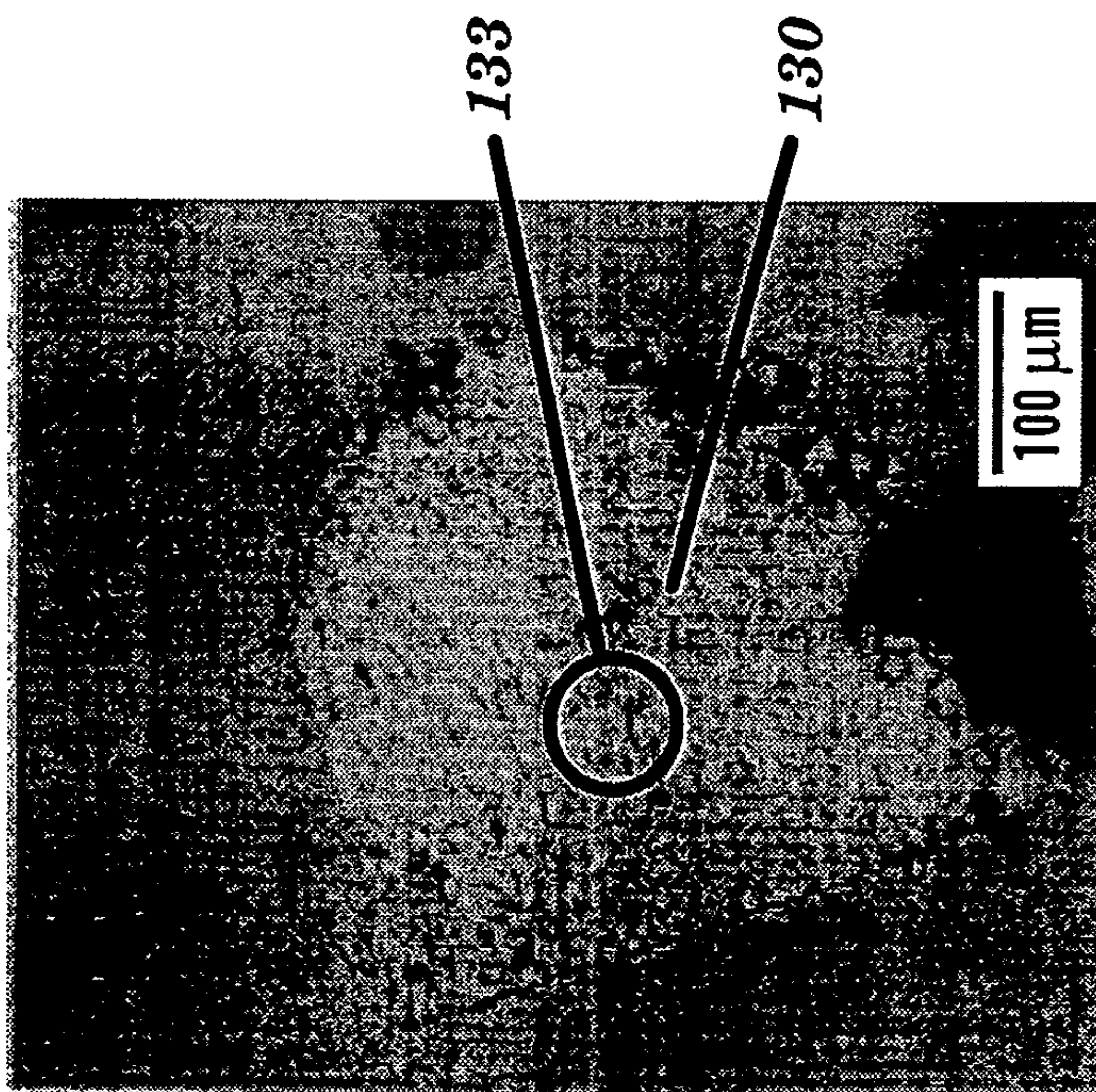

FIG. 13A

	PASTY RANGE ($\Delta T = T_{LIQUIDUS} - T_{SOLIDUS}$)	
SAC ALLOY	0.7 Cu	0.9 Cu
Sn2.1Ag x Cu	3.5	15.7
Sn2.3Ag x Cu	3.3	17.3
Sn2.5Ag x Cu	2.6	17.3
Sn2.7Ag x Cu	2	17.3
Sn2.9Ag x Cu	1.6	17.3

FIG. 14

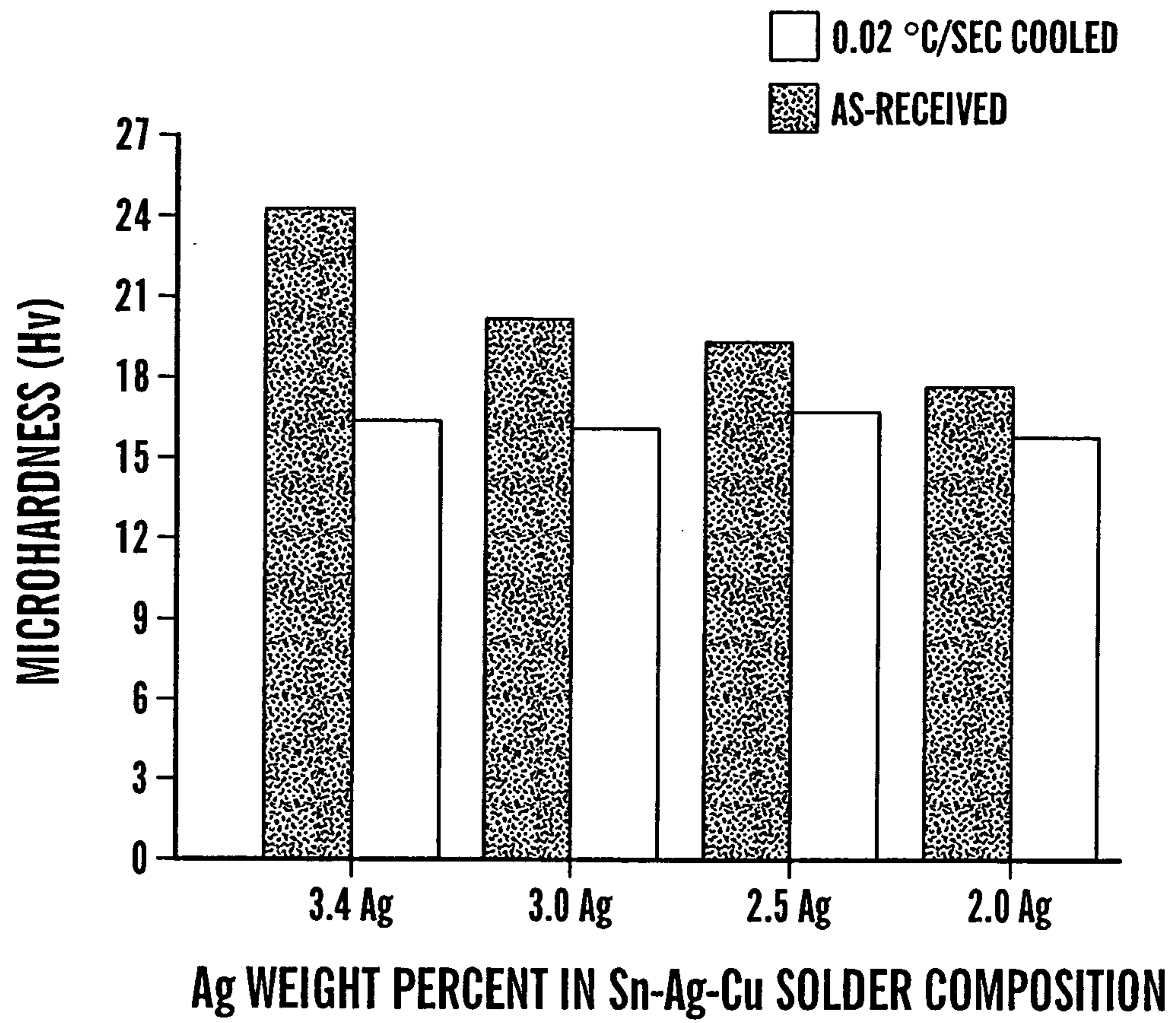

FIG. 15

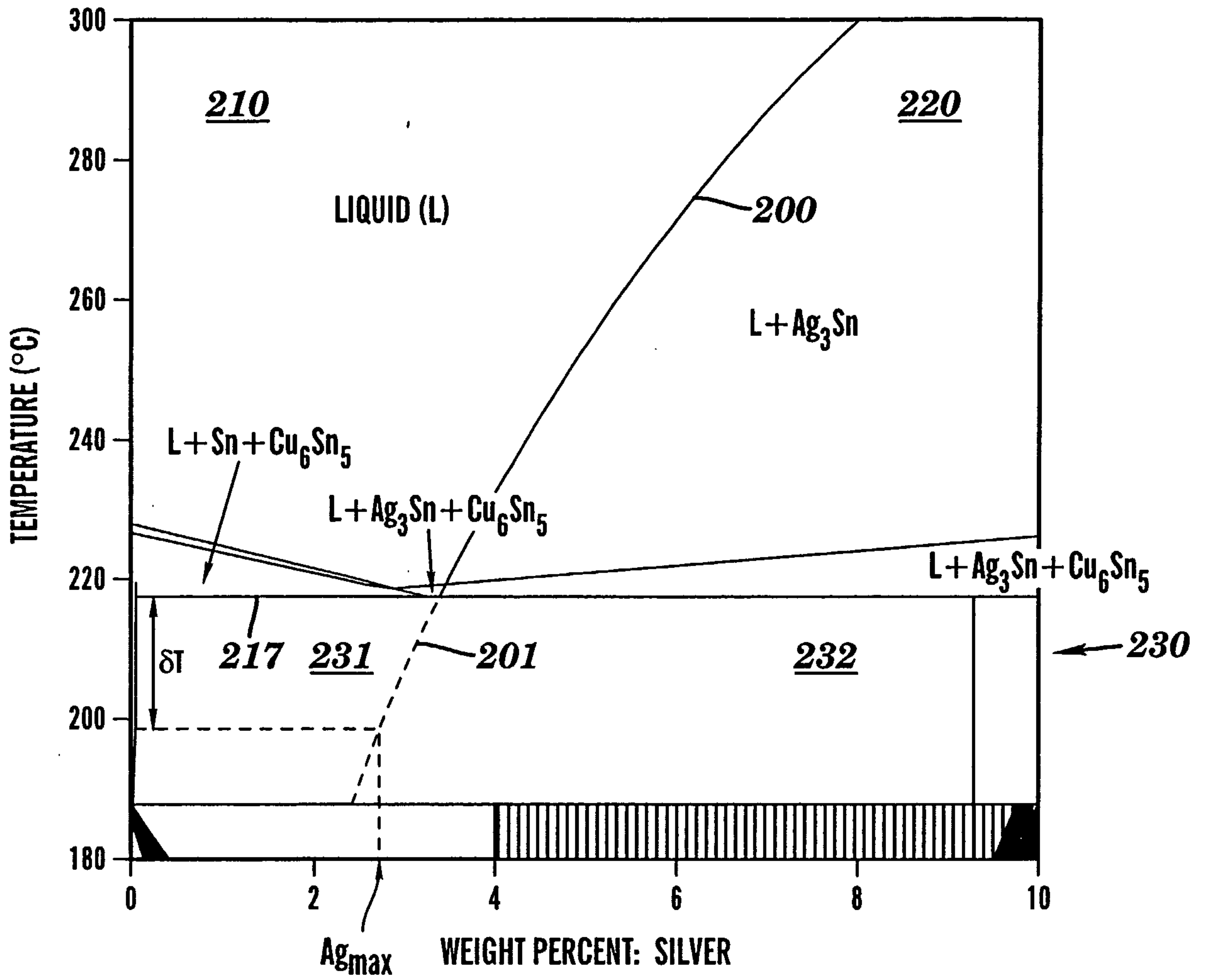

FIG. 16

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